Yasuhiko Arakawa

List of Publications by Year
in descending order

663	26,765	11235	11282
papers	citations	73 h-index	141 g-index

671	671	671	14665
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Impact of Quantum Dots on III-Nitride Lasers: A Theoretical Calculation on Linewidth Enhancement Factors. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-7.	1.9	1
2	InAs/InGaAs Quantum Dot Lasers on Multi-Functional Metamorphic Buffer Layers : Erratum. Optics Express, 2022, 30, 6617.	1.7	0
3	A large-scale single-mode array laser based on a topological edge mode. Nanophotonics, 2022, 11, 2169-2181.	2.9	8
4	Classification of in situ reflection high energy electron diffraction images by principal component analysis. Japanese Journal of Applied Physics, 2021, 60, SBBK03.	0.8	4
5	Recent progress in topological waveguides and nanocavities in a semiconductor photonic crystal platform [Invited]. Optical Materials Express, 2021, 11, 319.	1.6	55
6	Photoelectrochemical investigation of charge injection efficiency for quantum dot light-emitting diode. Applied Physics Letters, 2021, 118, .	1.5	7
7	Enhanced Single-Photon Emission from GaN Quantum Dots in Bullseye Structures. ACS Photonics, 2021, 8, 1656-1661.	3.2	23
8	Eâ€band InAs quantum dot laser on InGaAs metamorphic buffer layer with filter layer. Electronics Letters, 2021, 57, 567-568.	0.5	4
9	Experimental demonstration of topological slow light waveguides in valley photonic crystals. Optics Express, 2021, 29, 13441.	1.7	40
10	Microcavity-based generation of full PoincarÃ© beams with arbitrary skyrmion numbers. Physical Review Research, 2021, 3, .	1.3	31
11	Evaluation of degradation behavior in quantum dot light-emitting diode with different hole transport materials via transient electroluminescence. Applied Physics Letters, 2021, 118, .	1.5	9
12	Pure single-photon emission from an InGaN/GaN quantum dot. APL Materials, 2021, 9, .	2.2	8
13	GaAs-based microelectromechanical terahertz bolometers fabricated on high-resistivity Si substrates using wafer bonding technique. Applied Physics Letters, 2021, 119, .	1.5	11
14	InAs/InGaAs Quantum Dot Lasers on Multi-Functional Metamorphic Buffer Layers. Optics Express, 2021, 29, 29378.	1.7	7
15	Unidirectional output from a quantum-dot single-photon source hybrid integrated on silicon. Optics Express, 2021, 29, 37117.	1.7	16
16	The heat is on: towards the realization of non-cryogenic photonic quantum technologies. Materials for Quantum Technology, 2021, 1, 013001.	1.2	3
17	Chiral modes near exceptional points in symmetry broken H1 photonic crystal cavities. Physical Review Research, 2021, 3, .	1.3	10
18	Hybrid integrated light sources on silicon assembled by transfer printing. , 2021, , .		0

#	Article	IF	Citations
19	Single photon generation from AlGaN exciton localization centers exhibiting narrow spectral linewidths. APL Materials, 2021, 9, 121106.	2.2	2
20	Emission at 1.6â€‰Î¼m from InAs Quantum Dots in Metamorphic InGaAs Matrix. Physica Status Solidi (B): Basic Research, 2020, 257, 1900392.	0.7	7
21	Single-photon emission from isolated monolayer islands of InGaN. Light: Science and Applications, 2020, 9, 159.	7.7	20
22	Surface-passivated high-Q GaAs photonic crystal nanocavity with quantum dots. APL Photonics, 2020, 5, .	3.0	29
23	Reflectivity of three-dimensional GaAs photonic band-gap crystals of finite thickness. Physical Review B, 2020, 101, .	1.1	10
24	Excitation and emission dynamics of a single photon emitting InGaN quantum dot in a photonic horn structure. Superlattices and Microstructures, 2020, 145, 106575.	1.4	2
25	Progress in quantum-dot single photon sources for quantum information technologies: A broad spectrum overview. Applied Physics Reviews, 2020, 7, .	5.5	184
26	Classification of Reflection High-Energy Electron Diffraction Pattern Using Machine Learning. Crystal Growth and Design, 2020, 20, 5289-5293.	1.4	17
27	The 1200â€‰nmâ€Band InAs/GaAs Quantum Dot Intermixing by Dry Etching and Ion Implantation. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900851.	0.8	1
28	Fabrication and optical characterization of photonic crystal nanocavities with electrodes for gate-defined quantum dots. Japanese Journal of Applied Physics, 2020, 59, SGGI05.	0.8	6
29	In situ wavelength tuning of quantum-dot single-photon sources integrated on a CMOS-processed silicon waveguide. Applied Physics Letters, 2020, 116, .	1.5	29
30	Slow light waveguides in topological valley photonic crystals. Optics Letters, 2020, 45, 2648.	1.7	91
31	Active topological photonics. Nanophotonics, 2020, 9, 547-567.	2.9	170
32	High-Density Silicon Photonics Integrated Technology for Photonics-Electronics Convergence System. The Review of Laser Engineering, 2020, 42, 217.	0.0	0
33	Single photon source based on an InGaN quantum dot in a site-controlled optical horn structure. Applied Physics Letters, 2019, 115, .	1.5	11
34	Impact of quantum dots on III-nitride lasers: a theoretical calculation of threshold current densities. Japanese Journal of Applied Physics, 2019, 58, SCCC31.	0.8	4
35	Quantum dot lasers for silicon photonics. Semiconductors and Semimetals, 2019, 101, 91-138.	0.4	15
36	Photoluminescence properties as a function of growth mechanism for GaSb/GaAs quantum dots grown on Ge substrates. Journal of Applied Physics, 2019, 126, .	1.1	3

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37	III-nitride quantum dots as single photon emitters. Semiconductor Science and Technology, 2019, 34, 033001.	1.0	26
38	Observation of sharp emission lines from Zn-doped GaN. Japanese Journal of Applied Physics, 2019, 58, SCCB15.	0.8	1
39	Singleâ€photon emission from a further confined InGaN/GaN quantum disc via reverseâ€reaction growth. Quantum Engineering, 2019, 1, e20.	1.2	18
40	Elimination of anti-phase boundaries in a GaAs layer directly-grown on an on-axis Si(001) substrate by optimizing an AlGaAs nucleation layer. Japanese Journal of Applied Physics, 2019, 58, SBBE07.	0.8	15
41	Single Plasmon Generation in an InAs/GaAs Quantum Dot in a Transfer-Printed Plasmonic Microring Resonator. ACS Photonics, 2019, 6, 1106-1110.	3.2	15
42	Strongly Coupled Single-Quantum-Dotâ€“Cavity System Integrated on a CMOS-Processed Silicon Photonic Chip. Physical Review Applied, 2019, 11, .	1.5	38
43	Spectral diffusion time scales in InGaN/GaN quantum dots. Applied Physics Letters, 2019, 114, .	1.5	20
44	Quantum-dot single-photon source on a CMOS silicon photonic chip integrated using transfer printing. APL Photonics, 2019, 4, 036105.	3.0	48
45	High-temperature continuous-wave operation of directly grown InAs/GaAs quantum dot lasers on on-axis Si (001). Optics Express, 2019, 27, 2681.	1.7	43
46	Spin-dependent directional emission from a quantum dot ensemble embedded in an asymmetric waveguide. Optics Letters, 2019, 44, 3749.	1.7	3
47	Three-dimensional photonic crystal simultaneously integrating a nanocavity laser and waveguides. Optica, 2019, 6, 296.	4.8	20
48	Photonic crystal nanocavity based on a topological corner state. Optica, 2019, 6, 786.	4.8	274
49	Advances in Quantum Dot Lasers for High Efficiency and High Output Power Operation. The Review of Laser Engineering, 2019, 47, 210.	0.0	0
50	Topological Photonic Crystal Nanocavities. The Review of Laser Engineering, 2019, 47, 351.	0.0	0
51	Local tuning of transfer-printed quantum-dot single-photon sources on a CMOS silicon chip. , 2019, , .		0
52	Irinotecan and cisplatin therapy-induced neutropenia as a prognostic factor in patients with extensive-disease small cell lung cancer. Annals of Oncology, 2019, 30, ix27.	0.6	1
53	Large vacuum Rabi splitting between a single quantum dot and an H0 photonic crystal nanocavity. Applied Physics Letters, 2018, 112, .	1.5	27
54	Measurement of the Emission Lifetime of a GaN Interface Fluctuation Quantum Dot by Power Dependent Single Photon Dynamics. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700630.	0.8	5

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55	Low-Noise Characteristics on 1.3-Î¼m-Wavelength Quantum-Dot DFB Lasers Under External Optical Feedback. , 2018, , .		8
56	Topological photonic crystal nanocavity laser. Communications Physics, 2018, 1, .	2.0	154
57	InAs/GaAs quantum dot infrared photodetectors on onâ€axis Si (100) substrates. Electronics Letters, 2018, 54, 1395-1397.	0.5	9
58	Circularly Polarized Topological Edge States Derived from Optical Weyl Points in Semiconductor-Based Chiral Woodpile Photonic Crystals. Journal of the Physical Society of Japan, 2018, 87, 123401.	0.7	15
59	Improvement of single photon emission from InGaN QDs embedded in porous micropillars. Applied Physics Letters, 2018, 113, .	1.5	19
60	Highâ€•Q nanocavities in semiconductorâ€based threeâ€dimensional photonic crystals. Electronics Letters, 2018, 54, 305-307.	0.5	6
61	All MBE grown InAs/GaAs quantum dot lasers on on-axis Si (001). Optics Express, 2018, 26, 11568.	1.7	101
62	Transfer-printed single-photon sources coupled to wire waveguides. Optica, 2018, 5, 691.	4.8	76
63	Scheme for media conversion between electronic spin and photonic orbital angular momentum based on photonic nanocavity. Optics Express, 2018, 26, 21219.	1.7	8
64	Growth of InGaAs/GaAs nanowire-quantum dots on AlGaAs/GaAs distributed Bragg reflectors for laser applications. Journal of Crystal Growth, 2017, 468, 144-148.	0.7	13
65	Emission of Linearly Polarized Single Photons from Quantum Dots Contained in Nonpolar, Semipolar, and Polar Sections of Pencil-Like InGaN/GaN Nanowires. ACS Photonics, 2017, 4, 657-664.	3.2	44
66	Ultraclean Single Photon Emission from a GaN Quantum Dot. Nano Letters, 2017, 17, 2902-2907.	4.5	75
67	Optical coupling between atomically thin black phosphorus and a two dimensional photonic crystal nanocavity. Applied Physics Letters, 2017, 110, .	1.5	13
68	Demonstration of lasing oscillation in a plasmonic microring resonator containing quantum dots fabricated by transfer printing. Japanese Journal of Applied Physics, 2017, 56, 102001.	0.8	5
69	Manipulation of dynamic nuclear spin polarization in single quantum dots by photonic environment engineering. Physical Review B, 2017, 95, .	1.1	3
70	Method for generating a photonic NOON state with quantum dots in coupled nanocavities. Physical Review A, 2017, 96, .	1.0	15
71	Temperature dependence of the single photon emission from interface-fluctuation GaN quantum dots. Scientific Reports, 2017, 7, 16107.	1.6	12
72	Circularly polarized vacuum field in three-dimensional chiral photonic crystals probed by quantum dot emission. Physical Review B, 2017, 96, .	1.1	13

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73	UV/Ozone-assisted bonding for InAs/GaAs quantum dot lasers on Si. , 2017, , .		1
74	Progress in quantum dots for advanced photonics. , 2017, , .		0
75	Nanosecond-scale spectral diffusion in the single photon emission of a GaN quantum dot. AIP Advances, 2017, 7, .	0.6	18
76	A photonic crystal nanocavity with a quantum dot active region embedded by MBE regrowth. , 2017, , .		1
77	Imaging of topologically protected elastic mode in silica 1D phononic crystal via photoelastic effect. , 2017, , .		0
78	Double-stage guided-mode converter for pure TM-mode guiding in pillar photonic-crystal waveguide devices. Optics Express, 2017, 25, 17995.	1.7	5
79	Thresholdless quantum dot nanolaser. Optics Express, 2017, 25, 19981.	1.7	53
80	Semiconductor Three-Dimensional Photonic Crystals with Novel Layer-by-Layer Structures. Photonics, 2016, 3, 34.	0.9	6
81	P-117 Phase II study of combination chemotherapy of gemcitabine/S-1 with nafamostat mesilate for advanced unresectable pancreatic cancer. First report. Annals of Oncology, 2016, 27, ii34.	0.6	0
82	Self-assembled formation of GaAsP nano-apertures above InAs/GaAs quantum dots by the thermal diffusion of phosphorus. Physica Status Solidi (B): Basic Research, 2016, 253, 659-663.	0.7	2
83	InAs/GaAs quantum dot lasers with GaP strain-compensation layers grown by molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 958-964.	0.8	8
84	Single-photon emission at 1.5â€‰Î¼m from an InAs/InP quantum dot with highly suppressed multi-photon emission probabilities. Applied Physics Letters, 2016, 109, .	1.5	83
85	A Nanowire-Based Plasmonic Quantum Dot Laser. Nano Letters, 2016, 16, 2845-2850.	4.5	64
86	Direct modulation of InAs/GaAs quantum dot lasers on silicon at 60 Â°C. , 2016, , .		1
87	Direct modulation of 13 Î¼m quantum dot lasers on silicon at 60 Â°C. Optics Express, 2016, 24, 18428.	1.7	25
88	Yellow luminescence band in undoped GaN revealed by two-wavelength excited photoluminescence. Optical Materials, 2016, 60, 481-486.	1.7	31
89	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>p</mml:mi></mml:math>-shell carrier assisted dynamic nuclear spin polarization in single quantum dots at zero external magnetic field. Physical Review B, 2016, 93, .	1.1	3
90	Electroluminescence at 1.3 Âµm from InAs/GaAs quantum dots monolithically grown on Ge/Si substrate by metal organic chemical vapor deposition. Japanese Journal of Applied Physics, 2016, 55, 100304.	0.8	4

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91	(Invited) Fabrication of Ge Waveguides by Epitaxial Lateral Overgrowth toward Monolithic Integration of Light Sources. ECS Transactions, 2016, 75, 199-209.	0.3	1
92	Room-Temperature Observation of Trapped Exciton-Polariton Emission in GaN/AlGaN Microcavities with Air-Gap/III-Nitride Distributed Bragg Reflectors. ACS Photonics, 2016, 3, 1182-1187.	3.2	19
93	Single Photons from a Hot Solid-State Emitter at 350 K. ACS Photonics, 2016, 3, 543-546.	3.2	73
94	Linearly polarized single photons from small site-controlled GaN nanowire quantum dots. , 2016, , .		4
95	Influence of the relative positions of quantum dots and nanocavities on the optical coupling strength. , 2015, , .		0
96	Eigenvalue decomposition method for photon statistics of frequency-filtered fields and its application to quantum dot emitters. Physical Review A, 2015, 92, .	1.0	9
97	Effect of lateral electric field on the transition energies of neutral and charged excitons in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="normal">In</mml:mi><mml:mrow><mml:mn>0.5</mml:mn></mml:mrow></mml:msub><mml:msub><mml:mi mathvariant="normal">Ga</mml:mi><mml:mrow><mml:mn>0.5</mml:mn></mml:mrow></mml:msub><mml:mi mathvariant="normal">As</mml:mi><mml:mo>/</mml:mo><mml:mi mathvariant="normal">GaAs</mml:mi></mml:math>quantum dots. Physical Review B, 2015, 91, .	1.1	6
98	Spectral diffusion and its influence on the emission linewidths of site-controlled GaN nanowire quantum dots. Physical Review B, 2015, 92, .	1.1	53
99	Strong coupling in non-polar GaN/AlGaN microcavities with air-gap/III-nitride distributed Bragg reflectors. Applied Physics Letters, 2015, 107, .	1.5	20
100	Quantum key distribution over 120â€‰km using ultrahigh purity single-photon source and superconducting single-photon detectors. Scientific Reports, 2015, 5, 14383.	1.6	152
101	A direct evidence of allocating yellow luminescence band in undoped GaN by two-wavelength excited photoluminescence. Applied Physics Letters, 2015, 107, .	1.5	19
102	Excess carrier lifetime in epitaxially grown layers of germanium on silicon. , 2015, , .		2
103	Dominant nonradiative centers in InGaN single quantum well by timeâ€resolved and twoâ€wavelength excited photoluminescence. Physica Status Solidi (B): Basic Research, 2015, 252, 952-955.	0.7	4
104	Quantum Dot Laser for a Light Source of an Athermal Silicon Optical Interposer. Photonics, 2015, 2, 355-364.	0.9	5
105	Optical Characteristics of a Multichannel Hybrid Integrated Light Source for Ultra-High-Bandwidth Optical Interconnections. Photonics, 2015, 2, 1131-1138.	0.9	2
106	Design of efficient photo-elastic modulator using quasi-1D phononic crystal cavity. , 2015, , .		0
107	1.3-μm Quantum-dot lasers integrated with spot-size converter for improved coupling efficiency to waveguide. , 2015, , .		0
108	Low-Threshold near-Infrared GaAsâ€“AlGaAs Coreâ€“Shell Nanowire Plasmon Laser. ACS Photonics, 2015, 2, 165-171.	3.2	92

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109	Probing the Excitonic States of Site-Controlled GaN Nanowire Quantum Dots. Nano Letters, 2015, 15, 1047-1051.	4.5	10
110	Vacuum Rabi Spectra of a Single Quantum Emitter. Physical Review Letters, 2015, 114, 143603.	2.9	31
111	Direct Observation of Two-Step Photon Absorption in an InAs/GaAs Single Quantum Dot for the Operation of Intermediate-Band Solar Cells. Nano Letters, 2015, 15, 4483-4487.	4.5	25
112	Room-temperature lasing in a single nanowire with quantum dots. Nature Photonics, 2015, 9, 501-505.	15.6	159
113	First Demonstration of Athermal Silicon Optical Interposers With Quantum Dot Lasers Operating up to 125 Â°C. Journal of Lightwave Technology, 2015, 33, 1223-1229.	2.7	106
114	InAs/GaAs Quantum Dot Lasers on Silicon-on-Insulator Substrates by Metal-Stripe Wafer Bonding. IEEE Photonics Technology Letters, 2015, 27, 875-878.	1.3	26
115	Doping dependent blue shift and linewidth broadening of intersubband absorption in non-polar m-plane AlGaN/GaN multiple quantum wells. Applied Physics Letters, 2015, 107, .	1.5	25
116	High quality-factor Si/SiO_2-InP hybrid micropillar cavities with submicrometer diameter for 155-Î¼m telecommunication band. Optics Express, 2015, 23, 16264.	1.7	10
117	Asymmetric out-of-plane power distribution in a two-dimensional photonic crystal nanocavity. Optics Letters, 2015, 40, 3372.	1.7	8
118	Multi-channel Hybrid Integrated Light Source for Ultra-high-bandwidth Optical Interconnections and Its Structural Optimization for Low Power Consumption by Considering Thermal Interference between LD Arrays. Transactions of the Japan Institute of Electronics Packaging, 2014, 7, 94-103.	0.3	6
119	Observation of mid-infrared intersubband absorption in non-polar m-plane AlGaN/GaN multiple quantum wells. Applied Physics Letters, 2014, 105, .	1.5	30
120	Polarization properties of single zinc-blende GaN/AlN quantum dots. Physical Review B, 2014, 90, .	1.1	9
121	Athermal silicon optical interposers with quantum dot lasers operating from 25 to 125Â°C. Electronics Letters, 2014, 50, 1377-1378.	0.5	0
122	Position-controlled InP nanowires with 10â€“100â€‰Î¼m pitches using Au-deposited SiO2/InP patterned substrates. Applied Physics Letters, 2014, 104, .	1.5	17
123	High-density and wide-bandwidth optical interconnects with silicon optical interposers [Invited]. Photonics Research, 2014, 2, A1.	3.4	40
124	Manifestation of unconventional biexciton states in quantum dots. Nature Communications, 2014, 5, 5721.	5.8	44
125	Single-photon emission from cubic GaN quantum dots. Applied Physics Letters, 2014, 104, .	1.5	44
126	Impact of the dark path on quantum dot single photon emitters in small cavities. Physical Review Letters, 2014, 113, 143604.	2.9	5

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127	Highly uniform, multi-stacked InGaAs/GaAs quantum dots embedded in a GaAs nanowire. Applied Physics Letters, 2014, 105, .	1.5	26
128	Spectral diffusion in nitride quantum dots: Emission energy dependent linewidths broadening via giant builtâ€in dipole moments. Physica Status Solidi - Rapid Research Letters, 2014, 8, 408-413.	1.2	31
129	A Hybrid Integrated Light Source on a Silicon Platform Using a Trident Spot-Size Converter. Journal of Lightwave Technology, 2014, 32, 1329-1336.	2.7	152
130	Room-Temperature Triggered Single Photon Emission from a III-Nitride Site-Controlled Nanowire Quantum Dot. Nano Letters, 2014, 14, 982-986.	4.5	337
131	1064-nm DFB laser diode modules applicable to seeder for pulse-on-demand fiber laser systems. Optical Fiber Technology, 2014, 20, 714-724.	1.4	10
132	(Invited) Si Waveguide-Integrated High-Speed Ge Photodetector. ECS Transactions, 2014, 64, 723-727.	0.3	1
133	Excitonic complexes in single zinc-blende GaN/AlN quantum dots grown by droplet epitaxy. Applied Physics Letters, 2014, 105, .	1.5	9
134	InAs/GaAs quantum dot lasers metal-stripe-bonded onto SOI substrate. , 2014, , .		1
135	Optical anisotropy of m -plane nitride air-gap distributed Bragg reflector microcavities. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 840-843.	0.8	1
136	Measuring the second-order coherence of a nanolaser by intracavity frequency doubling. Physical Review A, 2014, 89, .	1.0	11
137	Identification of electric dipole moments of excitonic complexes in nitride-based quantum dots. Physical Review B, 2013, 88, .	1.1	25
138	Measurement of an Exciton Rabi Rotation in a SingleGaN/AlxGa1â^'xNNanowire-Quantum Dot Using Photoluminescence Spectroscopy: Evidence for Coherent Control. Physical Review Letters, 2013, 111, 057401.	2.9	26
139	Narrow spectral linewidth of single zinc-blende GaN/AlN self-assembled quantum dots. Applied Physics Letters, 2013, 103, 151109.	1.5	23
140	Strong exciton confinement in site-controlled GaN quantum dots embedded in nanowires. Applied Physics Letters, 2013, 103, 171907.	1.5	27
141	Site-controlled growth of single GaN quantum dots in nanowires by MOCVD. Journal of Crystal Growth, 2013, 370, 328-331.	0.7	24
142	Theoretical analysis of multilevel intermediate-band solar cells using a drift diffusion model. Journal of Applied Physics, 2013, 113, 243102.	1.1	6
143	Temperature Dependent Photoluminescence Excitation Spectroscopy of GaN Quantum Dots in Site Controlled GaN/AlGaN Nanowires. Japanese Journal of Applied Physics, 2013, 52, 08JL02.	0.8	6
144	Growth of highâ€quality InAs quantum dots embedded in GaAs nanowire structures on Si substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1496-1499.	0.8	6

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145	Self-frequency summing in photonic crystal nanocavity quantum dot lasers. , 2013, , .		0
146	Nonlinear photonics in single quantum dot-photonic crystal nanocavity couples systems. , 2013, , .		0
147	High performance inkjet-printed C60 fullerene thin-film transistors: Toward a low-cost and reproducible solution process. Organic Electronics, 2013, 14, 644-648.	1.4	21
148	Suppression of multi-photon emission in 1.5-µm quantum-dot single-photon source. , 2013, , .		0
149	Rim formation on non-elongated InAs quantum dots grown by partial cap and annealing process at low temperature. Journal of Crystal Growth, 2013, 378, 558-561.	0.7	1
150	Non-VLS growth of GaAs nanowires on silicon by a gallium pre-deposition technique. Journal of Crystal Growth, 2013, 378, 562-565.	0.7	3
151	Molecular beam epitaxial growths of high-optical-gain InAs quantum dots on GaAs for long-wavelength emission. Journal of Crystal Growth, 2013, 378, 459-462.	0.7	34
152	Large vacuum Rabi splitting in an H0 photonic crystal nanocavity-quantum dot system. , 2013, , .		0
153	Formation and optical properties of multi-stack InGaAs quantum dots embedded in GaAs nanowires by selective metalorganic chemical vapor deposition. Journal of Crystal Growth, 2013, 370, 299-302.	0.7	5
154	Shape evolution of low density InAs quantum dots in the partial capping process by using As2 source. Journal of Crystal Growth, 2013, 378, 549-552.	0.7	2
155	Growth of high-density 1.06-Î¼m InGaAs/GaAs quantum dots for high gain lasers by molecular beamepitaxy. Journal of Crystal Growth, 2013, 378, 627-630.	0.7	14
156	Design of large-bandwidth single-mode operation waveguides in silicon three-dimensional photonic crystals using two guided modes. Optics Express, 2013, 21, 12443.	1.7	3
157	Nanocavity-based self-frequency conversion laser. Optics Express, 2013, 21, 19778.	1.7	21
158	Differential receivers with highly -uniform MSM Germanium photodetectors capped by SiGe layer. Optics Express, 2013, 21, 23295.	1.7	11
159	Development of high-density single-mode polymer waveguides with low crosstalk for chip-to-chip optical interconnection. Optics Express, 2013, 21, 24231.	1.7	17
160	Giant optical rotation in a three-dimensional semiconductor chiral photonic crystal. Optics Express, 2013, 21, 29905.	1.7	23
161	Design of Si/SiO_2 micropillar cavities for Purcell-enhanced single photon emission at 155ÂÎ¼m from InAs/InP quantum dots. Optics Letters, 2013, 38, 3241.	1.7	16
162	Self-frequency summing in quantum dot photonic crystal nanocavity lasers. Applied Physics Letters, 2013, 103, 243115.	1.5	7

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163	Fabrication and optical properties of non-polar III-nitride air-gap distributed Bragg reflector microcavities. Applied Physics Letters, 2013, 103, .	1.5	21
164	Effect of SCH/barrier layer thickness on K-factor of quantum dot lasers. , 2013, , .		0
165	Enhancement of Valence Band Mixing in Individual InAs/GaAs Quantum Dots by Rapid Thermal Annealing. Japanese Journal of Applied Physics, 2013, 52, 125001.	0.8	9
166	Photoluminescence Excitation Spectroscopy on Single GaN Quantum Dots. Applied Physics Express, 2013, 6, 012102.	1.1	11
167	Shortâ€channel, highâ€mobility organic thinâ€film transistors with alkylated dinaphthothienothiophene. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1632-1635.	0.8	13
168	Design of highâ€Q nanocavity in threeâ€dimensional woodpile photonic crystal with vertically mirrorâ€symmetric structure. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1457-1460.	0.8	1
169	Highâ€Q AlN ladderâ€structure photonic crystal nanocavity fabricated by layer transfer. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1517-1520.	0.8	5
170	Cavity Quantum Electrodynamics in Semiconductors: Quantum Dot-Photonic Crystal Nanocavity Coupled Systems. The Review of Laser Engineering, 2013, 41, 485.	0.0	0
171	Surface Modification of Polydimethylsiloxane Using Low Pressure Chemical Vapour Deposition of Poly-Chloro-p-Xylene. Journal of Nano Research, 2012, 20, 129-142.	0.8	2
172	Fabrication of AlGaN Two-Dimensional Photonic Crystal Nanocavities by Selective Thermal Decomposition of GaN. Applied Physics Express, 2012, 5, 126502.	1.1	38
173	Demonstration of 125-Gbps optical interconnects integrated with lasers, optical splitters, optical modulators and photodetectors on a single silicon substrate. Optics Express, 2012, 20, B256.	1.7	53
174	13 Î¼m InAs/GaAs quantum dot lasers on Si rib structures with current injection across direct-bonded GaAs/Si heterointerfaces. Optics Express, 2012, 20, B315.	1.7	16
175	High Q H1 photonic crystal nanocavities with efficient vertical emission. Optics Express, 2012, 20, 28292.	1.7	39
176	High-efficiency InAs/GaAs quantum dot solar cells by metalorganic chemical vapor deposition. Applied Physics Letters, 2012, 100, .	1.5	131
177	High guided modeâ€“cavity mode coupling for an efficient extraction of spontaneous emission of a single quantum dot embedded in a photonic crystal nanobeam cavity. Physical Review B, 2012, 86, .	1.1	12
178	Site-controlled formation of InAs/GaAs quantum-dot-in-nanowires for single photon emitters. Applied Physics Letters, 2012, 100, .	1.5	47
179	Spectral fluctuations of excitonic transitions of InGaAs single quantum dots. Applied Physics Letters, 2012, 100, 022105.	1.5	5
180	Enhancement of carbon nanotube photoluminescence by photonic crystal nanocavities. Applied Physics Letters, 2012, 101, 141124.	1.5	53

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181	High-Q (>5000) AlN nanobeam photonic crystal cavity embedding GaN quantum dots. Applied Physics Letters, 2012, 100, .	1.5	24
182	III–V quantum dot lasers on Si substrates by wafer bonding. , 2012, , .		0
183	Enhancement of Light Emission from Silicon by Utilizing Photonic Nanostructures. IEICE Transactions on Electronics, 2012, E95-C, 206-212.	0.3	5
184	A single-electron probe for buried optically active quantum dot. AIP Advances, 2012, 2, 032103.	0.6	2
185	Silicon-based three-dimensional photonic crystal nanocavity laser with InAs quantum-dot gain. Applied Physics Letters, 2012, 101, .	1.5	8
186	High-efficiency InAs/GaAs quantum dot solar cells by MOCVD. , 2012, , .		0
187	Advances in quantum dot lasers for telecom and silicon photonics applications. , 2012, , .		0
188	Thin-film InAs/GaAs quantum dot solar cells layer-transferred onto Si substrates and flexible plastic films. , 2012, , .		18
189	Single quantum dot-photonic crystal nanocavity laser. , 2012, , .		0
190	Flexible thin-film InAs/GaAs quantum dot solar cells. Applied Physics Letters, 2012, 100, .	1.5	34
191	Improved stability in N-alkylated organic semiconductors for thin film transistors: Synthesis and characterization of N,Nâ€²-dialkylated dihydrodiazapentacene derivatives. Synthetic Metals, 2012, 162, 1264-1270.	2.1	11
192	Selective-area growth of thin GaN nanowires by MOCVD. Journal of Crystal Growth, 2012, 357, 58-61.	0.7	103
193	Cavity Quantum Electrodynamics and Lasing Oscillation in Single Quantum Dot-Photonic Crystal Nanocavity Coupled Systems. IEEE Journal of Selected Topics in Quantum Electronics, 2012, 18, 1818-1829.	1.9	31
194	High-Q AlN photonic crystal nanobeam cavities fabricated by layer transfer. Applied Physics Letters, 2012, 101, .	1.5	29
195	Exciton acoustic-phonon coupling in single GaN/AlN quantum dots. Physical Review B, 2012, 85, .	1.1	45
196	Influence of p-doping on the temperature dependence of InAs/GaAs quantum dot excited state radiative lifetime. Applied Physics Letters, 2012, 101, .	1.5	6
197	Selfâ€assembled m â€plane InGaN quantum dots: formation and shape evolution. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 613-615.	0.8	6
198	Shaking quantum dots. Nature Photonics, 2012, 6, 9-10.	15.6	8

#	Article	IF	Citations
199	Polarization-Insensitive Quantum Dot Semiconductor Optical Amplifiers Using Strain-Controlled Columnar Quantum Dots. Journal of Lightwave Technology, 2012, 30, 68-75.	2.7	35
200	Solution-Processed C60Single-Crystal Field-Effect Transistors. Japanese Journal of Applied Physics, 2012, 51, 11PD06.	0.8	3
201	Optical Properties of Site-Controlled InGaAs Quantum Dots Embedded in GaAs Nanowires by Selective Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2012, 51, 11PE13.	0.8	2
202	Proposal and design of III-V/Si hybrid lasers with current injection across conductive wafer-bonded heterointerfaces. , 2011, , .		0
203	Effect of cavity mode volume on photoluminescence from silicon photonic crystal nanocavities. Applied Physics Letters, 2011, 98, .	1.5	32
204	Detailed balance limit of the efficiency of multilevel intermediate band solar cells. Applied Physics Letters, 2011, 98, .	1.5	100
205	First demonstration of high density optical interconnects integrated with lasers, optical modulators, and photodetectors on single silicon substrate. Optics Express, 2011, 19, B159.	1.7	90
206	Novel III-V/Si hybrid laser structures with current injection across conductive wafer-bonded heterointerfaces: A proposal and analysis. IEICE Electronics Express, 2011, 8, 596-603.	0.3	11
207	Lasing Characteristics of a Quantum-Dot-3D-Photonic-Crystal-Nanocavity Coupled System: Interaction between Fully Confined Electrons and Photons. AIP Conference Proceedings, 2011, , .	0.3	0
208	Lasing oscillation in a three-dimensional photonic crystal nanocavity with a complete bandgap. Nature Photonics, 2011, 5, 91-94.	15.6	173
209	AlGaAs capping effect on InAs quantum dots self-assembled on GaAs. Physics Letters, Section A: General, Atomic and Solid State Physics, 2011, 375, 3517-3520.	0.9	7
210	Spontaneous Two-Photon Emission from a Single Quantum Dot. Physical Review Letters, 2011, 107, 233602.	2.9	124
211	New method to isolate and distribute photoluminescence emissions from InAs quantum dots over a wide-wavelength range. Journal of Crystal Growth, 2011, 323, 250-253.	0.7	2
212	Design of a highâ€Q H0 photonic crystal nanocavity for cavity QED. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 340-342.	0.8	4
213	Fabrication of electrically pumped InAs/GaAs quantum dot lasers on Si substrates by Auâ€mediated wafer bonding. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 319-321.	0.8	7
214	Effect of electronic structure on singleâ€photon emission in InAs/InP quantum dot with quasiâ€resonant excitation. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 417-419.	0.8	2
215	Effects of growth temperature of partial GaAs cap on InAs quantum dots in Inâ€flush process for single dot spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 248-250.	0.8	7
216	Growth of InAs/GaAs quantum dots on Si, Ge/Si and germanium-on-insulator-on-silicon (GeOI) substrates emitting in the 1.3 Î¼m band for silicon photonics. Journal of Crystal Growth, 2011, 315, 114-118.	0.7	12

#	Article	IF	Citations
217	Fabrication of high-Q silicon-based three-dimensional photonic crystal nanocavity and its lasing oscillation with InAs quantum-dot gain. , 2011, , .		1
218	Observation of Purcell effect in a 3D photonic crystal nanocavity with a single quantum dot. , 2011, , .		1
219	Formation of m-plane InGaN/GaN quantum dots using strain engineering of AlGaN/AlN interlayers. Applied Physics Letters, 2011, 99, .	1.5	13
220	Strong coupling between a photonic crystal nanobeam cavity and a single quantum dot. Applied Physics Letters, 2011, 98, .	1.5	84
221	Competing influence of an in-plane electric field on the Stark shifts in a semiconductor quantum dot. Applied Physics Letters, 2011, 99, 181109.	1.5	5
222	Structural and optical properties of m-plane GaN/AlGaN quantum wires grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2011, 99, 113106.	1.5	2
223	Metal Organic Chemical Vapor Deposition Growth of High Spectral Quality Site-Controlled InAs Quantum Dots UsingIn situPatterning. Applied Physics Express, 2011, 4, 112001.	1.1	5
224	Novel Solution Process for High-Mobility C$_{60}$ Fullerene Field-Effect Transistors. Applied Physics Express, 2011, 4, 121602.	1.1	12
225	High conductance bottom-contact pentacene thin-film transistors with gold-nickel adhesion layers. Applied Physics Letters, 2010, 97, 033306.	1.5	39
226	Esaki diodes live and learn. Proceedings of the Japan Academy Series B: Physical and Biological Sciences, 2010, 86, 451-453.	1.6	2
227	Formation of Ge-diffusion-suppressed GaAs layers and InAs quantum dots on Ge/Si substrates. Journal of Crystal Growth, 2010, 312, 2919-2922.	0.7	0
228	Growth of InAs/GaAs quantum dots on germanium-on-insulator-on-silicon substrate for silicon photonics. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2765-2767.	1.3	5
229	Magnetic field dependence of exciton fine structures in InAs/GaAs quantum dots: Exchange vs. Zeeman splittings. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2532-2535.	1.3	2
230	Observation of unique photon statistics of single artificial atom laser. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2489-2492.	1.3	3
231	Suppression of indefinite peaks in InAs/GaAs quantum dot spectrum by low temperature capping in the indium-flush method. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2753-2756.	1.3	11
232	Charged and neutral biexcitonâ€“exciton cascade in a single quantum dot within a photonic bandgap. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2563-2566.	1.3	6
233	Design, fabrication and optical characterization of GaAs photonic crystal nanocavity lasers with InAs quantum dots gain wafer-bonded onto Si substrates. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2560-2562.	1.3	1
234	Fabrication and characterization of a vertical pillar structure including a self-assembled quantum dot and a quantum well. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2592-2594.	1.3	2

#	Article	IF	Citations
235	Enhancement of photoluminescence from germanium by utilizing air-bridge-type photonic crystal slab. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2556-2559.	1.3	8
236	Synthesis and investigation of Ï€-conjugated azomethine self-assembled multilayers by layer-by-layer growth. Thin Solid Films, 2010, 518, 5115-5120.	0.8	4
237	Acoustic phonon effects on telecommunicationâ€band quantum dot exciton Rabi oscillation. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2578-2581.	0.8	0
238	Laser oscillation in a strongly coupled single-quantum-dotâ€“nanocavity system. Nature Physics, 2010, 6, 279-283.	6.5	300
239	Transmission Experiment of Quantum Keys over 50 km Using High-Performance Quantum-Dot Single-Photon Source at 1.5 Âµm Wavelength. Applied Physics Express, 2010, 3, 092802.	1.1	58
240	Spin dynamics of excited trion states in a single InAs quantum dot. Physical Review B, 2010, 81, .	1.1	14
241	Switching operation of lasing wavelength in mid-infrared ridge-waveguide quantum cascade lasers coupled with microcylindrical cavity. Applied Physics Letters, 2010, 96, .	1.5	10
242	Zero-cell photonic crystal nanocavity laser with quantum dot gain. Applied Physics Letters, 2010, 97, .	1.5	19
243	Exciton fine-structure splitting in GaN/AlN quantum dots. Physical Review B, 2010, 81, .	1.1	59
244	High-Q design of semiconductor-based ultrasmall photonic crystal nanocavity. Optics Express, 2010, 18, 8144.	1.7	43
245	Electrically pumped 13 Î¼m room-temperature InAs/GaAs quantum dot lasers on Si substrates by metal-mediated wafer bonding and layer transfer. Optics Express, 2010, 18, 10604.	1.7	84
246	Ground state lasing at 1.30 Âµm from InAs/GaAs quantum dot lasers grown by metalâ€“organic chemical vapor deposition. Nanotechnology, 2010, 21, 105604.	1.3	12
247	Fabrication of InAs/GaAs quantum dot solar cells with enhanced photocurrent and without degradation of open circuit voltage. Applied Physics Letters, 2010, 96, .	1.5	281
248	Modulation of Hepatocarcinoma Cell Morphology and Activity by Parylene-C Coating on PDMS. PLoS ONE, 2010, 5, e9667.	1.1	18
249	Quantitative Estimation of Exchange Interaction Energy Using Two-Electron Vertical Double Quantum Dots. Physical Review Letters, 2009, 102, 146802.	2.9	24
250	Threshold voltage control of bottom-contact n-channel organic thin-film transistors using modified drain/source electrodes. Applied Physics Letters, 2009, 94, .	1.5	61
251	Hybrid p-n junction light-emitting diodes based on sputtered ZnO and organic semiconductors. Applied Physics Letters, 2009, 95, .	1.5	58
252	Light-matter interaction in single quantum dot with photonic crystal nanocavity. , 2009, , .		0

#	Article	IF	Citations
253	Vacuum Rabi splitting with a single quantum dot embedded in a H1 photonic crystal nanocavity. Applied Physics Letters, 2009, 94, .	1.5	41
254	InAs/Sb∶GaAs quantum dot solar cells grown by metal organic chemical vapor deposition. , 2009, , .		4
255	Current-gain cutoff frequencies above 10 MHz for organic thin-film transistors with high mobility and low parasitic capacitance. Applied Physics Letters, 2009, 95, .	1.5	51
256	Investigation of the Spectral Triplet in Strongly Coupled Quantum Dotâ€“Nanocavity System. Applied Physics Express, 2009, 2, 122301.	1.1	20
257	Low-voltage-operating organic complementary circuits based on pentacene and C60 transistors. Thin Solid Films, 2009, 517, 2079-2082.	0.8	31
258	Biexcitonic photocurrent induced by twoâ€photon process at a telecommunication band. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1445-1448.	0.8	0
259	Controlling the size of InAs quantum dots on Si1â^'xGex/Si(001) by metalorganic vapor-phase epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 165, 103-106.	1.7	0
260	Resonant photoluminescence from Ge self-assembled dots in optical microcavities. Journal of Crystal Growth, 2009, 311, 883-887.	0.7	7
261	Spin-Related Current Suppression in a Semiconductor Quantum Dot Spin-Diode Structure. Physical Review Letters, 2009, 102, 236806.	2.9	39
262	Demonstration of high-Qâ€^(>8600) three-dimensional photonic crystal nanocavity embedding quantum dots. Applied Physics Letters, 2009, 94, .	1.5	35
263	Photonic band-edge micro lasers with quantum dot gain. Optics Express, 2009, 17, 640.	1.7	14
264	Room temperature continuous wave operation of InAs/GaAs quantum dot photonic crystal nanocavity laser on silicon substrate. Optics Express, 2009, 17, 7036.	1.7	55
265	Photonic crystal nanocavity laser with a single quantum dot gain. Optics Express, 2009, 17, 15975.	1.7	110
266	Interface properties of InAs quantum dots produced by antimony surfactant-mediated growth: Etching of segregated antimony and its impact on the photoluminescence and lasing characteristics. Applied Physics Letters, 2009, 94, .	1.5	30
267	Dual luminescence from organic/inorganic hybrid p-n junction light-emitting diodes. Applied Physics Letters, 2009, 94, .	1.5	17
268	Photonic crystal nanocavity lasers with InAs quantum dots bonded onto silicon substrates. , 2009, , .		0
269	Prerequisites of nanocavities for single artificial atom laser. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2831-2834.	0.8	0
270	Lowâ€voltageâ€operating fullerene C₆₀ thinâ€film transistors with various surface treatments. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3181-3183.	0.8	7

#	Article	IF	Citations
271	Elastic and inelastic tunneling through oneâ€electron and twoâ€electron states in a vertical double quantum dot. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2854-2857.	0.8	3
272	Telecom singleâ€photon source with horn structure. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2699-2703.	0.8	6
273	Processâ€free estimation of threshold current density of InAs quantum dot laser. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2935-2937.	0.8	1
274	Preface: phys. stat. sol. (c) 5/9. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2693-2696.	0.8	0
275	Formation of InAs1â^'xSbx quantum dots on vicinal InP(001) for 1.55-Î¼m DFB laser applications. Journal of Crystal Growth, 2008, 310, 2999-3003.	0.7	1
276	Dislocation reduction of GaSb on GaAs by metalorganic chemical vapor deposition with epitaxial lateral overgrowth. Journal of Crystal Growth, 2008, 310, 4843-4845.	0.7	10
277	Optimizing the GaAs capping layer growth of 1.3Î¼m InAs/GaAs quantum dots by a combined two-temperature and annealing process at low temperatures. Journal of Crystal Growth, 2008, 310, 5469-5472.	0.7	13
278	Singletâ€“triplet transition induced by Zeeman energy in weakly coupled vertical double quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1139-1141.	1.3	3
279	Ultra-low threshold photonic crystal nanocavity laser. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1800-1803.	1.3	21
280	Effects of accumulated strain on the surface and optical properties of stacked 1.3Î¼m InAs/GaAs quantum dot structures. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2182-2184.	1.3	11
281	Observation of very narrow fine-structure splittings in self-assembled quantum dots by photocurrent spectroscopy. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2192-2194.	1.3	0
282	Proton radiation effects in quantum dot lasers. Applied Surface Science, 2008, 255, 676-678.	3.1	6
283	Coupling of quantum-dot light emission with a three-dimensional photonic-crystal nanocavity. Nature Photonics, 2008, 2, 688-692.	15.6	166
284	Pentacene-based organic field-effect transistors. Journal of Physics Condensed Matter, 2008, 20, 184011.	0.7	176
285	Growth of InAsâ^•Sb:GaAs quantum dots on silicon substrate with high density and efficient light emission in the 1.3Î¼m band. Applied Physics Letters, 2008, 92, .	1.5	36
286	Demonstration of transverse-magnetic dominant gain in quantum dot semiconductor optical amplifiers. Applied Physics Letters, 2008, 92, .	1.5	36
287	Quantum-Dot Semiconductor Optical Amplifiers With Polarization-Independent Gains in 1.5-mum Wavelength Bands. IEEE Photonics Technology Letters, 2008, 20, 1908-1910.	1.3	34
288	CW Lasing at 1.35 mum From Ten InAsâ€“Sbâ€‰:â€‰GaAs Quantum-Dot Layers Grown by Metalâ€“Organic Chemical Vapor Deposition. IEEE Photonics Technology Letters, 2008, 20, 827-829.	1.3	17

#	Article	IF	Citations
289	Increase of Q-factor in photonic crystal H1-defect nanocavities after closing of photonic bandgap with optimal slab thickness. Optics Express, 2008, 16, 448.	1.7	36
290	Coherently driven semiconductor quantum dot at a telecommunication wavelength. Optics Express, 2008, 16, 13949.	1.7	18
291	Design of high-Q photonic crystal microcavities with a graded square lattice for application to quantum cascade lasers. Optics Express, 2008, 16, 21321.	1.7	14
292	Exciton dynamics in current-injected single quantum dot at 1.55Î¼m. Applied Physics Letters, 2008, 92, 161104.	1.5	17
293	Two-Dimensional Photonic Crystal Resist Membrane Nanocavity Embedding Colloidal Dot-in-a-Rod Nanocrystals. Nano Letters, 2008, 8, 260-264.	4.5	38
294	Organic/inorganic hybrid complementary circuits based on pentacene and amorphous indium gallium zinc oxide transistors. Applied Physics Letters, 2008, 93, .	1.5	64
295	Growth of Columnar Quantum Dots by Metalorganic Vapor-Phase Epitaxy for Semiconductor Optical Amplifiers. Japanese Journal of Applied Physics, 2008, 47, 2888-2892.	0.8	8
296	First Demonstration of Electrically Driven 1.55 Âµm Single-Photon Generator. Japanese Journal of Applied Physics, 2008, 47, 2880-2883.	0.8	25
297	40-Gbit/s Operation of Ultracompact Photodetector-Integrated Dispersion Compensator Based on One-Dimensional Photonic Crystals. Japanese Journal of Applied Physics, 2008, 47, 6672-6674.	0.8	4
298	Advances in quantum dots for semiconductor lasers and single photon emitters: From science to practical implementation. , 2008, , .		0
299	Advances in quantum dots and 2D/3D photonic crystal nanocavity based on micro-machining technology. , 2008, , .		0
300	Optical properties of columnar InAs quantum dots on InP for semiconductor optical amplifiers. Applied Physics Letters, 2008, 93, 121908.	1.5	23
301	Bottom-contact fullerene C60 thin-film transistors with high field-effect mobilities. Applied Physics Letters, 2008, 93, 033313.	1.5	46
302	Tunneling magnetoresistance effect in a few-electron quantum-dot spin valve. Applied Physics Letters, 2008, 93, 222107.	1.5	11
303	Growth of high-uniformity InAsâˆ•GaAs quantum dots with ultralow density below 107cmâˆ’2 and emission above 1.3Î¼m. Applied Physics Letters, 2008, 92, 163101.	1.5	17
304	Electric field modulation of exciton recombination in InAs/GaAs quantum dots emitting at 1.3Î¼m. Journal of Applied Physics, 2008, 104, 013504.	1.1	6
305	Enhanced photon emission and absorption of single quantum dot in resonance with two modes in photonic crystal nanocavity. Applied Physics Letters, 2008, 93, 183114.	1.5	15
306	Enhancement of Room Temperature Photoluminescence from InAs Quantum Dots by Irradiating Mn. Japanese Journal of Applied Physics, 2007, 46, L801-L803.	0.8	0

#	Article	IF	Citations
307	Ground state lasing at 1.34Î¼m from InAsâ•GaAs quantum dots grown by antimony-mediated metal organic chemical vapor deposition. Applied Physics Letters, 2007, 90, 241110.	1.5	39
308	AlN air-bridge photonic crystal nanocavities demonstrating high quality factor. Applied Physics Letters, 2007, 91, 051106.	1.5	55
309	High-performance fullerene C60 thin-film transistors operating at low voltages. Applied Physics Letters, 2007, 91, 183514.	1.5	21
310	High performance flexible pentacene thin-film transistors fabricated on titanium silicon oxide gate dielectrics. Applied Physics Letters, 2007, 90, 163514.	1.5	24
311	Kondo effect in a semiconductor quantum dot coupled to ferromagnetic electrodes. Applied Physics Letters, 2007, 91, .	1.5	70
312	An optical horn structure for single-photon source using quantum dots at telecommunication wavelength. Journal of Applied Physics, 2007, 101, 081720.	1.1	93
313	Observation of enhanced photoluminescence from silicon photonic crystal nanocavity at room temperature. Applied Physics Letters, 2007, 91, .	1.5	60
314	Demonstration of High-Q Photonic Crystal H1-defect Nanocavities after Closing of Photonic Bandgap. , 2007, , .		0
315	Systematic Study of the Effects of Modulation p-Doping on 1.3-$mu{hbox {m}}$ Quantum-Dot Lasers. IEEE Journal of Quantum Electronics, 2007, 43, 1129-1139.	1.0	65
316	High performance n-channel thin-film transistors with an amorphous phase C60 film on plastic substrate. Applied Physics Letters, 2007, 91, .	1.5	22
317	Resonant photoluminescence from crystalline Si with photonic crystal nanocavity structures. , 2007, , .		0
318	Low-voltage-operating complementary inverters with C60 and pentacene transistors on glass substrates. Applied Physics Letters, 2007, 91, 053505.	1.5	65
319	Photonic Crystal Nanocavity for Highly Efficient Lasers and Light Sources. Conference Proceedings - Lasers and Electro-Optics Society Annual Meeting-LEOS, 2007, , .	0.0	0
320	Effects of rapid thermal annealing on the emission properties of highly uniform self-assembled InAsâ•GaAs quantum dots emitting at 1.3Î¼m. Applied Physics Letters, 2007, 90, 111912.	1.5	25
321	Coulomb blockade in a self-assembled GaN quantum dot. Applied Physics Letters, 2007, 90, 162109.	1.5	13
322	Prospects of Quantum Dots for Advanced Nanophotonic Devices. , 2007, , .		0
323	Surface reconstructions on Sb-irradiated GaAs(001) formed by molecular beam epitaxy. Microelectronics Journal, 2007, 38, 620-624.	1.1	9
324	Effect of antimony on the density of InAs/Sb:GaAs(100) quantum dots grown by metalorganic chemical-vapor deposition. Journal of Crystal Growth, 2007, 298, 548-552.	0.7	32

#	Article	IF	Citations
325	Evaluation of incorporation efficiency of group V source gases in metal organic chemical vapor deposition of GaInNAs for high quality 1.21Î¼m quantum-well ridge wave guide lasers. Journal of Crystal Growth, 2007, 298, 658-662.	0.7	0
326	The Electronic Properties of DNA Bases. Small, 2007, 3, 1539-1543.	5.2	51
327	Development of a two-dimensional dual pendulum thrust stand for Hall thrusters. Review of Scientific Instruments, 2007, 78, 115108.	0.6	24
328	Molecular analysis of Clostridium difficile at a university teaching hospital in Japan: a shift in the predominant type over a five-year period. European Journal of Clinical Microbiology and Infectious Diseases, 2007, 26, 695-703.	1.3	65
329	Localized excitation of InGaAs quantum dots by utilizing a photonic crystal nanocavity. Applied Physics Letters, 2006, 88, 141108.	1.5	14
330	High-performance pentacene thin-film transistors with high dielectric constant gate insulators. Applied Physics Letters, 2006, 89, 223525.	1.5	28
331	Si Photonic Wire Waveguide Devices. IEEE Journal of Selected Topics in Quantum Electronics, 2006, 12, 1371-1379.	1.9	141
332	High density InAsâˆ•GaAs quantum dots with enhanced photoluminescence intensity using antimony surfactant-mediated metal organic chemical vapor deposition. Applied Physics Letters, 2006, 89, 183124.	1.5	50
333	Tunable Optical Notch Filter Realized by Shifting the Photonic Bandgap in a Silicon Photonic Crystal Line-Defect Waveguide. IEEE Photonics Technology Letters, 2006, 18, 2614-2616.	1.3	20
334	Artificial control of optical gain polarization by stacking quantum dot layers. Applied Physics Letters, 2006, 88, 211106.	1.5	75
335	Room temperature continuous-wave lasing in photonic crystal nanocavity. Optics Express, 2006, 14, 6308.	1.7	186
336	Cavity Resonant Excitation of InGaAs Quantum Dots in Photonic Crystal Nanocavities. Japanese Journal of Applied Physics, 2006, 45, 6091-6095.	0.8	11
337	Development of high-yield fabrication technique for MEMS-PhC devices. IEICE Electronics Express, 2006, 3, 39-43.	0.3	3
338	Atomistic Insights for InAs Quantum Dot Formation on GaAs(001) using STM within a MBE Growth Chamber. Small, 2006, 2, 386-389.	5.2	45
339	Advances in growth and optical properties of GaN-based quantum dots. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 3512-3522.	0.8	13
340	Degenerate four-wave mixing spectroscopy of GaN films on various substrates. Physica Status Solidi (B): Basic Research, 2006, 243, 1560-1563.	0.7	3
341	Transient pumpâ€“probe measurements for polarized excitons in strained GaN epitaxial layers. Physica Status Solidi (B): Basic Research, 2006, 243, 1564-1567.	0.7	3
342	A gallium nitride single-photon source operating at 200â€‰K. Nature Materials, 2006, 5, 887-892.	13.3	388

#	Article	IF	Citations
343	Heteroepitaxial growth of InAs on GaAs(001) by in situ STM located inside MBE growth chamber. Microelectronics Journal, 2006, 37, 1498-1504.	1.1	22
344	Focusing characteristics of optical fiber axicon microlens for near-field spectroscopy: Dependence of tip apex angle. Optics Communications, 2006, 267, 264-270.	1.0	27
345	Quantum confined Stark effect in single self-assembled GaN/AlN quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 148-151.	1.3	30
346	Magneto-optical single dot spectroscopy of GaSb/GaAs type II quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 152-154.	1.3	2
347	Temperature-dependent conductance of quasi-one-dimensional electrons in a novel constricted channel with corrugated interfaces. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 337-340.	1.3	0
348	Electron transport and shell structures of single InAs quantum dots probed by nanogap electrodes. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 187-190.	1.3	0
349	Advances in photonic crystals with MEMS and with semiconductor quantum dots. Laser Physics, 2006, 16, 223-231.	0.6	3
350	Development of a Method for Preparing a Highly Reactive and Stable, Recyclable and Environmentally Benign Organopalladium Catalyst Supported on Sulfur-Terminated Gallium Arsenide(001): A Three-Component Catalyst, {Pd}-S-GaAs(001), and its Properties. Advanced Synthesis and Catalysis, 2006, 348, 1063-1070.	2.1	25
351	Development of Electrically Driven Single-Quantum-Dot Device at Optical Fiber Bands. Japanese Journal of Applied Physics, 2006, 45, 3621-3624.	0.8	13
352	Sulfur-Terminated GaAs-Supported Pd Catalyst for the Heck Reaction. Synfacts, 2006, 2006, 1070-1070.	0.0	1
353	In SituScanning Tunneling Microscope Observation of InAs Wetting Layer Formation on GaAs(001) during Molecular Beam Epitaxy Growth at 500 Â°C. Japanese Journal of Applied Physics, 2006, 45, L777-L779.	0.8	25
354	Highly Reactive Organopalladium Catalyst Formed on Sulfur-Terminated GaAs(001)-(2 Ã— 6) Surface. Japanese Journal of Applied Physics, 2006, 45, L475-L477.	0.8	10
355	Enhancement of light emission from single quantum dot in photonic crystal nanocavity by using cavity resonant excitation. Applied Physics Letters, 2006, 89, 241124.	1.5	21
356	Unconventional quantum-confined Stark effect in a singleGaNquantum dot. Physical Review B, 2006, 73, .	1.1	47
357	Highly efficient optical pumping of photonic crystal nanocavity lasers using cavity resonant excitation. Applied Physics Letters, 2006, 89, 161111.	1.5	27
358	Controlling Polarization of 1.55-Âµm Columnar InAs Quantum Dots with Highly Tensile-Strained InGaAsP Barriers on InP(001). Japanese Journal of Applied Physics, 2006, 45, L1244-L1246.	0.8	18
359	Resonant-Wavelength Control in Visible-Light Range of Organic Photonic Crystal Nanocavities. Japanese Journal of Applied Physics, 2006, 45, 6112-6115.	0.8	0
360	Optical Control of Transmittance by Photo-Induced Absorption Effect in InGaN/GaN Structures. Japanese Journal of Applied Physics, 2005, 44, 7238-7243.	0.8	3

#	Article	IF	Citations
361	Highly uniform self-assembled InAs/GaAs quantum dots emitting at 1.3Î¼m by metalorganic chemical vapor deposition. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 77-80.	1.3	2
362	InAs/AlAs quantum dots with InGaAs insertion layer: dependence of the indium composition and the thickness. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 138-142.	1.3	4
363	Single InAs/InP quantum dot spectroscopy in 1.3â€“1.55Î¼m telecommunication band. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 185-189.	1.3	11
364	Strain distribution and electronic states in stacked InAs/GaAs quantum dots with dot spacing 0â€“. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 217-221.	1.3	30
365	Optical Polarization Properties of InAs/GaAs Quantum Dot Semiconductor Optical Amplifier. Japanese Journal of Applied Physics, 2005, 44, 2528-2530.	0.8	11
366	Lasing at 1.28 /spl mu/m of InAs-GaAs quantum dots with AlGaAs cladding layer grown by metal-organic chemical vapor deposition. IEEE Journal of Selected Topics in Quantum Electronics, 2005, 11, 1027-1034.	1.9	17
367	Quantum and transport scattering times in modulation-doped AlxGa1-xN/GaN single quantum wells. Applied Physics A: Materials Science and Processing, 2005, 80, 39-42.	1.1	0
368	Conformation and Local Environment Dependent Conductance of DNA Molecules. Small, 2005, 1, 1168-1172.	5.2	29
369	Observation of 1.55 Âµm Light Emission from InAs Quantum Dots in Photonic Crystal Microcavity. Japanese Journal of Applied Physics, 2005, 44, 2579-2583.	0.8	12
370	Dispersion Compensation in 40 Gb/s Non-Return-to-Zero Optical Transmission System Using Coupled-Cavity Photonic Crystals. Japanese Journal of Applied Physics, 2005, 44, L1282-L1284.	0.8	4
371	Internal Strain of Self-Assembled InxGa1-xAs Quantum Dots Calculated to Realize Transverse-Magnetic-Mode-Sensitive Interband Optical Transition at Wavelengths of 1.5 Âµm bands. Japanese Journal of Applied Physics, 2005, 44, 6312-6316.	0.8	11
372	Three-Dimensional Imaging of GaN Films Using Transient Two-Photon Absorption Excited by Near-Infrared Laser Pulses. Japanese Journal of Applied Physics, 2005, 44, L535-L538.	0.8	3
373	Enhanced Luminance Efficiency of Organic Light-Emitting Diodes with Two-Dimensional Photonic Crystals. Japanese Journal of Applied Physics, 2005, 44, 2844-2848.	0.8	30
374	Optical add-drop multiplexers based on Si-wire waveguides. Applied Physics Letters, 2005, 86, 191107.	1.5	37
375	Enhanced light emission from an organic photonic crystal with a nanocavity. Applied Physics Letters, 2005, 87, 151119.	1.5	34
376	Long-lived electron spins in InxGa1â^'xN multiquantum well. Applied Physics Letters, 2005, 86, 242103.	1.5	22
377	Photon correlation studies of single GaN quantum dots. Applied Physics Letters, 2005, 87, 051916.	1.5	71
378	Biexciton and exciton dynamics in single InGaN quantum dots. Nanotechnology, 2005, 16, 1477-1481.	1.3	24

#	Article	IF	Citations
379	Shell structures in self-assembled InAs quantum dots probed by lateral electron tunneling structures. Applied Physics Letters, 2005, 87, 203109.	1.5	58
380	Nonlinear-Optic Silicon-Nanowire Waveguides. Japanese Journal of Applied Physics, 2005, 44, 6541-6545.	0.8	66
381	Room temperature continuous wave lasing in InAs quantum-dot microdisks with air cladding. Optics Express, 2005, 13, 1615.	1.7	44
382	Compact 1 Ã— N thermo-optic switches based on silicon photonic wire waveguides. Optics Express, 2005, 13, 10109.	1.7	131
383	Recent progress in self-assembled quantum-dot optical devices for optical telecommunication: temperature-insensitive 10â€‰Gbâ€‰sâ^'1directly modulated lasers and 40â€‰Gbâ€‰sâ^'1signal-regenerative amplifiers224 Journal Physics D: Applied Physics, 2005, 38, 2126-2134.	1.3	
384	Optical directional coupler based on Si-wire waveguides. IEEE Photonics Technology Letters, 2005, 17, 585-587.	1.3	125
385	An ultrawide-band semiconductor optical amplifier having an extremely high penalty-free output power of 23 dBm achieved with quantum dots. IEEE Photonics Technology Letters, 2005, 17, 1614-1616.	1.3	178
386	Thermooptic switch based on photonic-crystal line-defect waveguides. IEEE Photonics Technology Letters, 2005, 17, 2083-2085.	1.3	36
387	Single-Photon Generation in the 1.55-Âµm Optical-Fiber Band from an InAs/InP Quantum Dot. Japanese Journal of Applied Physics, 2005, 44, L620-L622.	0.8	120
388	Group-Delay Properties of Coupled-Defect Structures in Photonic Crystals. Japanese Journal of Applied Physics, 2004, 43, L449-L452.	0.8	9
389	Enhancement of Cavity-Qin a Quasi-Three-Dimensional Photonic Crystal. Japanese Journal of Applied Physics, 2004, 43, 1990-1994.	0.8	8
390	Reflection Characteristics of Coupled-Defect-Type Photonic Crystals. Japanese Journal of Applied Physics, 2004, 43, 6104-6107.	0.8	0
391	Effects of InGaAs Insertion Layer on the Properties of High-Density InAs/AlAs Quantum Dots. Japanese Journal of Applied Physics, 2004, 43, 3828-3830.	0.8	0
392	Transition Energy Control via Strain in Single Quantum Dots Embedded in Micromachined Air-Bridge. Japanese Journal of Applied Physics, 2004, 43, 2069-2072.	0.8	0
393	Manipulation of electronic states in single quantum dots by micromachined air-bridge. Applied Physics Letters, 2004, 84, 1392-1394.	1.5	8
394	Narrow photoluminescence linewidth (<17â€‰meV) from highly uniform self-assembled InAs/GaAs quantum dots grown by low-pressure metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 84, 2817-2819.	1.5	60
395	Lasing characteristics of InAs quantum-dot microdisk from 3K to room temperature. Applied Physics Letters, 2004, 85, 1326-1328.	1.5	30
396	1.5-Î¼m-wavelength light guiding in waveguides in square-lattice-of-rod photonic crystal slab. Applied Physics Letters, 2004, 84, 4298-4300.	1.5	81

#	Article	IF	Citations
397	Improvement of the uniformity of self-assembled InAs quantum dots grown on InGaAsâˆ•GaAs by low-pressure metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 85, 2753-2755.	1.5	23
398	Picosecond dynamics of spin-related optical nonlinearities in InxGa1â^'xAs multiple quantum wells at 1064 nm. Applied Physics Letters, 2004, 84, 1043-1045.	1.5	7
399	Carrier relaxation in closely stacked InAs quantum dots. Journal of Applied Physics, 2004, 96, 150-154.	1.1	18
400	Fabrication of InAs quantum dots on InP(100) by metalorganic vapor-phase epitaxy for 1.55 Î¼m optical device applications. Applied Physics Letters, 2004, 85, 4331.	1.5	43
401	Temperature-Insensitive Eye-Opening under 10-Gb/s Modulation of 1.3-Âµm P-Doped Quantum-Dot Lasers without Current Adjustments. Japanese Journal of Applied Physics, 2004, 43, L1124-L1126.	0.8	163
402	Non-classical Photon Emission from a Single InAs/InP Quantum Dot in the 1.3-Âµm Optical-Fiber Band. Japanese Journal of Applied Physics, 2004, 43, L993-L995.	0.8	71
403	Control of InxGa1-xAs Capping Layer Induced Optical Polarization in Edge-Emitting Photoluminescence of InAs Quantum Dots. Japanese Journal of Applied Physics, 2004, 43, 1978-1980.	0.8	2
404	Enhanced Optical Properties of High-Density (>1011/cm2) InAs/AlAs Quantum Dots by Hydrogen Passivation. Japanese Journal of Applied Physics, 2004, 43, 2118-2121.	0.8	4
405	Differential Absorption in InGaN Multiple Quantum Wells and Epilayers Induced by Blue-Violet Laser Diode. Japanese Journal of Applied Physics, 2004, 43, L340-L342.	0.8	3
406	Group Delay of a Coupled-Defect Waveguide in a Photonic Crystal. Optical Review, 2004, 11, 300-302.	1.2	2
407	Selective excitation of self-assembled quantum dots by using shaped pulse. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 180-183.	1.3	2
408	Numerical analysis of DFB lasing action in photonic crystals with quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 814-819.	1.3	3
409	Photo-induced absorption change for InGaN film by violet laser diode. Physica Status Solidi (B): Basic Research, 2004, 241, 2703-2707.	0.7	1
410	Time-integrated and time-resolved photoluminescence studies of InGaN quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 568-572.	0.8	1
411	Time-resolved gain saturation dynamics in InGaN multi-quantum well structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2508-2511.	0.8	0
412	UV photoluminescence from GaN self-assembled quantum dots on AlxGa1â€“xN surfaces grown by metalorganic chemical vapor deposition. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2516-2519.	0.8	3
413	Soluble Polymer Complexes Having AlQ3-Type Pendent Groups. Macromolecular Rapid Communications, 2004, 25, 1171-1174.	2.0	30
414	Simultaneous determination of the index and absorption gratings in multiple quantum well photorefractive devices designed for laser ultrasonic sensor. Optics Communications, 2004, 242, 7-12.	1.0	8

#	Article	IF	Citations
415	MOCVD-grown InGaN-channel HEMT structures with electron mobility of over. Journal of Crystal Growth, 2004, 272, 278-284.	0.7	52
416	Formation of high-density GaN self-assembled quantum dots by MOCVD. Journal of Crystal Growth, 2004, 272, 161-166.	0.7	6
417	Dynamics of single InGaN quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 285-289.	1.3	24
418	Long-wavelength luminescence from GaSb quantum dots grown on GaAs substrates. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 275-278.	1.3	13
419	Structural and optical properties of high-density (>1011/cm2) InAs QDs with varying Al(Ga)As matrix layer thickness. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 279-284.	1.3	7
420	Spectroscopy on single columns of vertically aligned InAs quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 409-413.	1.3	3
421	Time-of-Flight Measurement of Lateral Carrier Mobility in Organic Thin Films. Japanese Journal of Applied Physics, 2004, 43, 2326-2329.	0.8	41
422	Formation of ultrahigh-density InAs/AlAs quantum dots by metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 84, 1877-1879.	1.5	21
423	Exciton and biexciton luminescence from single hexagonal GaNâˆ•AlN self-assembled quantum dots. Applied Physics Letters, 2004, 85, 64-66.	1.5	92
424	Photon lifetime dependence of modulation efficiency and K factor in 1.3Î¼m self-assembled InAsâˆ•GaAs quantum-dot lasers: Impact of capture time and maximum modal gain on modulation bandwidth. Applied Physics Letters, 2004, 85, 4145-4147.	1.5	88
425	Spin and carrier relaxation in resonantly excited InGaAs MQWs. Semiconductor Science and Technology, 2004, 19, S339-S341.	1.0	7
426	Weak anti-localization of the two-dimensional electron gas in modulation-doped AlxGa1âˆ’xNâˆ•GaN heterostructures with two subbands occupation. Applied Physics Letters, 2004, 85, 3125-3127.	1.5	16
427	Formation and optical properties of stacked GaN self-assembled quantum dots grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 85, 1262-1264.	1.5	42
428	Control of optical polarization anisotropy in edge emitting luminescence of InAs/GaAs self-assembled quantum dots. Applied Physics Letters, 2004, 84, 1820-1822.	1.5	54
429	InAsâˆ•GaAs self-assembled quantum-dot lasers grown by metalorganic chemical vapor depositionâ€"Effects of postgrowth annealing on stacked InAs quantum dots. Applied Physics Letters, 2004, 85, 1024-1026.	1.5	47
430	Novel Palladium Catalyst Supported on GaAs(001) Passivated by Ammonium Sulfide. Chemistry Letters, 2004, 33, 1208-1209.	0.7	20
431	In situ scanning tunneling microscopy of InAs quantum dots on GaAs() during molecular beam epitaxial growth. Surface Science, 2003, 544, 234-240.	0.8	14
432	Time-resolved gain dynamics in InGaN MQWs using a Kerr gate. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 255-257.	1.3	1

#	Article	IF	Citations
433	Subbands transport of the two-dimensional electron gas in AlxGa1â^'xN/GaN heterostructures. Optical Materials, 2003, 23, 139-141.	1.7	1
434	Ohmic contact and interfacial reaction of Ti/Al/Pt/Au metallic multi-layers on n-AlxGa1â^'xN/GaN heterostructures. Optical Materials, 2003, 23, 197-201.	1.7	12
435	Effect of strain variation on photoluminescence from InGaAs quantum dots in air-bridge structures. Physica Status Solidi (B): Basic Research, 2003, 238, 289-292.	0.7	2
436	Long-lived excitons up to 1Î¼s in GaN/AlN self-assembled quantum dots. Physica Status Solidi (B): Basic Research, 2003, 240, 388-391.	0.7	1
437	Stranskiâ€“Krastanow growth of stacked GaN quantum dots with intense photoluminescence. Physica Status Solidi (B): Basic Research, 2003, 240, 322-325.	0.7	7
438	Effect of thermal treatment on structure of GaN self-assembled quantum dots grown by MOCVD. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1101-1104.	0.8	4
439	Polarization field and electronic states of GaN pyramidal quantum dots in AlN. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1169-1172.	0.8	7
440	Multisubband transport of the two-dimensional electron gas in AlxGa1â^'xN/GaN heterostructures. Journal of Applied Physics, 2003, 93, 1651-1655.	1.1	17
441	Low threshold current operation of self-assembled InAsâ^•GaAs quantum dot lasers by metal organic chemicalvapour deposition. Electronics Letters, 2003, 39, 1130.	0.5	42
442	Ectopically expressed PDX-1 in liver initiates endocrine and exocrine pancreas differentiation but causes dysmorphogenesis. Biochemical and Biophysical Research Communications, 2003, 310, 1017-1025.	1.0	115
443	Time-resolved dynamics in single InGaN quantum dots. Applied Physics Letters, 2003, 83, 2674-2676.	1.5	49
444	High-resolution near-field spectroscopy of InAs single quantum dots at 70 K. Applied Physics Letters, 2003, 83, 3024-3026.	1.5	11
445	Nearly diffraction-limited focusing of a fiber axicon microlens. Review of Scientific Instruments, 2003, 74, 4969-4971.	0.6	55
446	Transport properties of two-dimensional electron gas in different subbands in triangular quantum wells at AlxGa1â^'xN/GaN heterointerfaces. Applied Physics Letters, 2003, 82, 1872-1874.	1.5	16
447	Strain-induced modifications of the electronic states of InGaAs quantum dots embedded in bowed airbridge structures. Journal of Applied Physics, 2003, 94, 6812-6817.	1.1	14
448	Two-photon absorption and multiphoton-induced photoluminescence of bulk GaN excited below the middle of the band gap. Applied Physics Letters, 2003, 82, 4714-4716.	1.5	25
449	Magnetoresistance oscillations induced by intersubband scattering of two-dimensional electron gas in Al[sub 0.22]Ga[sub 0.78]N/GaN heterostructures. Journal of Applied Physics, 2003, 94, 5420.	1.1	33
450	Organic light-emitting diodes driven by pentacene-based thin-film transistors. Applied Physics Letters, 2003, 83, 3410-3412.	1.5	111

#	Article	IF	Citations
451	Nondegenerate pump and probe spectroscopy in InGaN thin films. Journal of Applied Physics, 2003, 94, 6468-6471.	1.1	8
452	Size-dependent radiative decay time of excitons in GaN/AlN self-assembled quantum dots. Applied Physics Letters, 2003, 83, 984-986.	1.5	75
453	Organic Transistor Circuits for Application to Organic Light-Emitting-Diode Displays. Japanese Journal of Applied Physics, 2003, 42, 2483-2487.	0.8	27
454	Optical Characteristics of Two-Dimensional Photonic Crystal Slab Nanocavities with Self-Assembled InAs Quantum Dots for 1.3 Âµm Light Emission. Japanese Journal of Applied Physics, 2003, 42, 2391-2394.	0.8	6
455	Optical anisotropy of self-assembled InGaAs quantum dots embedded in wall-shaped and air-bridge structures. Applied Physics Letters, 2002, 81, 3954-3956.	1.5	9
456	Observation of enhanced spontaneous emission coupling factor in nitride-based vertical-cavity surface-emitting laser. Applied Physics Letters, 2002, 80, 722-724.	1.5	36
457	Investigation of the Polarization-Induced Charges in Modulation-Doped AlxGa1-xN/GaN Heterostructures through Capacitanceâ€“Voltage Profiling and Simulation. Japanese Journal of Applied Physics, 2002, 41, 2531-2535.	0.8	6
458	X-chromosomal localization of mammalian Y-linked genes in two XO species of the Ryukyu spiny rat. Cytogenetic and Genome Research, 2002, 99, 303-309.	0.6	66
459	Line Broadening of Photoluminescence Excitation Resonances in Single Self-Assembled Quantum Dots. Japanese Journal of Applied Physics, 2002, 41, L1464-L1466.	0.8	4
460	Influence of Ferroelectric Polarization on the Properties of Two-Dimensional Electron Gas in Pb(Zr0.53Ti0.47)O3/AlxGa1-xN/GaN Structures. Japanese Journal of Applied Physics, 2002, 41, 2528-2530.	0.8	23
461	Cyclotron resonance and magnetotransport measurements in AlxGa1â^'xN/GaN heterostructures for x=0.15â€“0.30. Applied Physics Letters, 2002, 80, 431-433.	1.5	17
462	High-density and size-controlled GaN self-assembled quantum dots grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2002, 80, 3937-3939.	1.5	122
463	Near-field optical photoluminescence microscopy of high-density InAs/GaAs single quantum dots. Applied Physics Letters, 2002, 80, 2779-2781.	1.5	21
464	Progress in GaN-based quantum dots for optoelectronics applications. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 823-832.	1.9	116
465	Introduction to the issue on nanostructures and quantum dots. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 969-971.	1.9	0
466	Observation of Intersubband Transition from the First to the Third Subband (e1-e3) in GaN/AlGaN Quantum Wells. Physica Status Solidi A, 2002, 192, 27-32.	1.7	7
467	UV Photoluminescence from Size-Controlled GaN Quantum Dots Grown by MOCVD. Physica Status Solidi A, 2002, 192, 33-38.	1.7	14
468	InGaN Vertical Microcavity LEDs with a Si-Doped AlGaN/GaN Distributed Bragg Reflector. Physica Status Solidi A, 2002, 194, 403-406.	1.7	17

#	Article	IF	Citations
469	Saturation of gain in In0.02Ga0.98N/In0.16Ga0.84N MQW plasmas. Physica B: Condensed Matter, 2002, 314, 47-51.	1.3	0
470	Observation of dip structures in PLE spectra of a highly excited single self-assembled quantum dot. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 151-154.	1.3	2
471	Electronic structure of piezoelectric In0.2Ga0.8N quantum dots in GaN calculated using a tight-binding method. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 15, 169-181.	1.3	97
472	Dynamics and gain in highly-excited InGaN MQWs. Current Applied Physics, 2002, 2, 321-326.	1.1	1
473	Photorefractive InGaAs/GaAs multiple quantum wells in the Franzâ€“Keldysh geometry. Journal of Applied Physics, 2001, 89, 5889-5896.	1.1	13
474	Photorefractive multiple quantum wells at 1064â€‰â€‰nm. Optics Letters, 2001, 26, 22.	1.7	17
475	Misorientation-angle dependence of GaN layers grown on a-plane sapphire substrates by metalorganic chemical vapor deposition. Applied Physics Letters, 2001, 79, 1992-1994.	1.5	34
476	InGaAs/GaAs photorefractive multiple quantum well device in quantum confined Stark geometry. Applied Physics B: Lasers and Optics, 2001, 72, 685-689.	1.1	5
477	New SNOM sensor using optical feedback in a VCSEL-based compound-cavity. Sensors and Actuators A: Physical, 2001, 87, 113-123.	2.0	21
478	Excitonic resonant photorefractive devices around 1.06 Î¼m. Optical Materials, 2001, 18, 183-185.	1.7	1
479	Near 1.3 ?m Emission at Room Temperature from InAsSb/GaAs Self-Assembled Quantum Dots on GaAs Substrates. Physica Status Solidi (B): Basic Research, 2001, 224, 139-142.	0.7	19
480	Correlation Effects in Strain-Induced Quantum Dots. Physica Status Solidi (B): Basic Research, 2001, 224, 361-366.	0.7	2
481	Uniform Array of GaN Quantum Dots in AlGaN Matrix by Selective MOCVD Growth. Physica Status Solidi (B): Basic Research, 2001, 228, 187-190.	0.7	9
482	Self-Assembled Growth of GaN Quantum Dots Using Low-Pressure MOCVD. Physica Status Solidi (B): Basic Research, 2001, 228, 191-194.	0.7	1
483	Extremely Slow Relaxation Process of a Yellow-Luminescence-Related State in GaN Revealed by Two-Wavelength Excited Photoluminescence. Physica Status Solidi (B): Basic Research, 2001, 228, 433-436.	0.7	2
484	Structure Dependence of Electron Mobility in GaN/AlGaN Multiple Quantum Wells. Physica Status Solidi A, 2001, 188, 877-880.	1.7	4
485	Over 1.5 Î¼m light emission from InAs quantum dots embedded in InGaAs strain-reducing layer grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2001, 78, 3469-3471.	1.5	259
486	Analysis of gain saturation in In0.02Ga0.98N/In0.16Ga0.84N multiple quantum wells. Applied Physics Letters, 2001, 79, 3434-3436.	1.5	24

#	Article	IF	Citations
487	Influence of Coulomb and Exchange Interaction on Quantum Dot Magnetoluminescence up to B = 45 T. Physica Status Solidi A, 2000, 178, 263-268.	1.7	3
488	Photoluminescence of GaN Quantum Wells with AlGaN Barriers of High Aluminium Content. Physica Status Solidi A, 2000, 180, 339-343.	1.7	8
489	Formation of uniform 10-nm-scale InGaN quantum dots by selective MOCVD growth and their micro-photoluminescence intensity images. Journal of Crystal Growth, 2000, 221, 576-580.	0.7	15
490	Spectroscopic discrimination of non-radiative centers in quantum wells by two wavelength excited photoluminescence. Journal of Crystal Growth, 2000, 210, 238-241.	0.7	2
491	Photoluminescence from two-dimensional electron gas in modulation-doped AlxGa1â^'xN/GaN heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 939-943.	1.3	2
492	MOCVD growth of a stacked InGaN quantum dot structure and its lasing oscillation at room temperature. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 944-948.	1.3	4
493	Resonant Raman scattering of optical phonons in self-assembled quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 8, 328-332.	1.3	3
494	Effects of electronâ€“hole correlation in quantum dots under high magnetic field (up to 45 T). Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 346-349.	1.3	2
495	Enhancement of the Coulomb correlations in type-II quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 393-397.	1.3	24
496	Absence of nonradiative recombination centers in modulation-doped quantum wells revealed by two-wavelength excited photoluminescence. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 563-566.	1.3	6
497	Area-Controlled Growth of InAs Quantum Dots by Selective MOCVD. Japanese Journal of Applied Physics, 2000, 39, 2344-2346.	0.8	4
498	Characterization of Proton-Irradiated InGaAs/GaAs Multiple Quantum Well Structures by Nonresonant Transient Four-Wave Mixing Technique. Japanese Journal of Applied Physics, 2000, 39, 5781-5787.	0.8	5
499	Occupation of the double subbands by the two-dimensional electron gas in the triangular quantum well atAlxGa1â^'xN/GaNheterostructures. Physical Review B, 2000, 62, R7739-R7742.	1.1	58
500	Selective growth of InGaN quantum dot structures and their microphotoluminescence at room temperature. Applied Physics Letters, 2000, 76, 3212-3214.	1.5	102
501	Influence of strain relaxation of the AlxGa1â^'xN barrier on transport properties of the two-dimensional electron gas in modulation-doped AlxGa1â^'xN/GaN heterostructures. Applied Physics Letters, 2000, 76, 2746-2748.	1.5	72
502	Time-resolved photoluminescence of GaN/Al[sub 0.5]Ga[sub 0.5]N quantum wells. Applied Physics Letters, 2000, 77, 1005.	1.5	25
503	Area-controlled growth of InAs quantum dots and improvement of density and size distribution. Applied Physics Letters, 2000, 77, 3382-3384.	1.5	44
504	Narrow photoluminescence peaks from localized states in InGaN quantum dot structures. Applied Physics Letters, 2000, 76, 2361-2363.	1.5	131

#	Article	IF	Citations
505	Photoluminescence from sub-nanometer-thick GaN/Al0.8Ga0.2N quantum wells. Applied Physics Letters, 2000, 77, 1336-1338.	1.5	9
506	Near-field coherent excitation spectroscopy of InGaAs/GaAs self-assembled quantum dots. Applied Physics Letters, 2000, 76, 3887-3889.	1.5	56
507	Growth of InGaN self-assembled quantum dots and their application to lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2000, 6, 475-481.	1.9	23
508	Near-field spectroscopy of a single InGaAs self-assembled quantum dot. IEEE Journal of Selected Topics in Quantum Electronics, 2000, 6, 528-533.	1.9	7
509	Introduction to the issue on nanostructures and quantum dots. IEEE Journal of Selected Topics in Quantum Electronics, 2000, 6, 405-407.	1.9	0
510	Effect of carrier confinement on photoluminescence from modulation-doped AlxGa1â^'xN/GaN heterostructures. Applied Physics Letters, 2000, 76, 679-681.	1.5	30
511	Lifetime of Confined LO Phonons in Quantum Dots and Its Impact on Phonon Bottleneck Issue. Japanese Journal of Applied Physics, 1999, 38, 473-476.	0.8	9
512	Room-temperature lasing oscillation in an InGaN self-assembled quantum dot laser. Applied Physics Letters, 1999, 75, 2605-2607.	1.5	82
513	Phonon bottleneck in quantum dots:â€ƒRole of lifetime of the confined optical phonons. Physical Review B, 1999, 59, 5069-5073.	1.1	180
514	Growth Condition Dependence of the Photoluminescence Properties of InxGa1-xN/InyGa1-yN Multiple Quantum Wells Grown by MOCVD. Japanese Journal of Applied Physics, 1999, 38, 2613-2616.	0.8	8
515	Microphotoluminescence Intensity Images of InGaN Single Quantum Wells. Japanese Journal of Applied Physics, 1999, 38, L1216-L1218.	0.8	15
516	Confined optical phonons in semiconductor quantum dots. Solid State Communications, 1999, 109, 351-356.	0.9	2
517	Near-field spectroscopy of single self-assembled InAs quantum dots: Observation of energy relaxation process. Microelectronic Engineering, 1999, 47, 111-113.	1.1	1
518	Screening of the Polarization Field in InGaN Single Quantum Wells. Physica Status Solidi (B): Basic Research, 1999, 216, 423-426.	0.7	3
519	Influence of AlxGa1â€"xN Thickness on Transport Properties of a Two-Dimensional Electron Gas in Modulation Doped AlxGa1â€"xN/GaN Single Heterostructures. Physica Status Solidi (B): Basic Research, 1999, 216, 755-759.	0.7	5
520	MOCVD Growth and Optical Characterization of Stacked InGaN Quantum Dots for Laser Applications. Physica Status Solidi A, 1999, 176, 629-633.	1.7	6
521	Growth and Structural Characterization of InGaN Vertical Cavity Surface Emitting Lasers Operating at Room Temperature. Physica Status Solidi A, 1999, 176, 63-66.	1.7	8
522	Structural and optical properties of type II GaSb/GaAs self-assembled quantum dots grown by molecular beam epitaxy. Journal of Applied Physics, 1999, 85, 8349-8352.	1.1	128

#	Article	IF	Citations
523	Nanometer-scale InGaN self-assembled quantum dots grown by metalorganic chemical vapor deposition. Applied Physics Letters, 1999, 74, 383-385.	1.5	197
524	Optical linewidths in an individual quantum dot. Physical Review B, 1999, 60, 1915-1920.	1.1	64
525	Atomic structure and phase stability ofInxGa1â^'xNrandom alloys calculated using a valence-force-field method. Physical Review B, 1999, 60, 1701-1706.	1.1	104
526	Room Temperature Lasing at Blue Wavelengths in Gallium Nitride Microcavities. Science, 1999, 285, 1905-1906.	6.0	237
527	Efficient Carrier Relaxation Mechanism in InGaAs/GaAs Self-Assembled Quantum Dots Based on the Existence of Continuum States. Physical Review Letters, 1999, 82, 4114-4117.	2.9	341
528	Electron-Hole Correlation in Quantum Dots under a High Magnetic Field (up to 45 T). Physical Review Letters, 1999, 83, 4832-4835.	2.9	18
529	Design and analysis of micromechanical tunable interferometers for WDM free-space optical interconnection. Journal of Lightwave Technology, 1999, 17, 19-25.	2.7	16
530	Resonant photorefractive effect in InGaAs/GaAs multiple quantum wells. Optics Letters, 1999, 24, 321.	1.7	13
531	Distribution of below-gap states in undoped GaAs/AlGaAs quantum wells revealed by two-wavelength excited photoluminescence. Journal of Luminescence, 1998, 79, 39-46.	1.5	9
532	Dielectric function associated with dispersive optic-vibrations. Solid State Communications, 1998, 108, 211-213.	0.9	8
533	Light emission from individual InAs/GaAs self-assembled quantum dots excited by tunneling current injection. Solid-State Electronics, 1998, 42, 1079-1082.	0.8	0
534	Near-field optical spectroscopy of self-assembled quantum dots: NSOM apparatus for measuring the features of single dots. Solid-State Electronics, 1998, 42, 1083-1086.	0.8	9
535	Selective growth of GaAs quantum dots and vertical quantum wires in two-dimensional V-grooves. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 15-18.	1.3	2
536	Near-field spectroscopy of quantum wires grown by selective growth method. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 987-990.	1.3	3
537	Density Control of GaSb/GaAs Self-assembled Quantum Dots (â^¼25nm) Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1998, 37, L203-L205.	0.8	44
538	Seeded self-assembled GaAs quantum dots grown in two-dimensional V grooves by selective metalâ€“organic chemical-vapor deposition. Applied Physics Letters, 1998, 72, 800-802.	1.5	27
539	Light emission from individual self-assembled InAs/GaAs quantum dots excited by tunneling current injection. Applied Physics Letters, 1998, 73, 1460-1462.	1.5	28
540	Highly reflective GaN/Al0.34Ga0.66N quarter-wave reflectors grown by metal organic chemical vapor deposition. Applied Physics Letters, 1998, 73, 3653-3655.	1.5	109

#	Article	IF	Citations
541	Anharmonic decay of confined optical phonons in quantum dots. Physical Review B, 1998, 57, 12285-12290.	1.1	63
542	Strain-energy distribution and electronic structure of InAs pyramidal quantum dots with uncovered surfaces: Tight-binding analysis. Physical Review B, 1998, 57, 13016-13019.	1.1	36
543	Optical spectroscopy of self-assembled type II GaSb/GaAs quantum dot structures grown by molecular beam epitaxy. Applied Physics Letters, 1998, 72, 2856-2858.	1.5	35
544	Microphotoluminescence spectroscopy of vertically stackedInxGa1â^'xAs/GaAsquantum wires. Physical Review B, 1998, 58, 1962-1966.	1.1	19
545	Polarized photoluminescence spectroscopy of single self-assembled InAs quantum dots. Physical Review B, 1998, 58, R10147-R10150.	1.1	55
546	Microprobe spectroscopy of localized exciton states in IIâ€“VI quantum wells. Applied Physics Letters, 1998, 73, 148-150.	1.5	10
547	Near-field magneto-optical spectroscopy of single self-assembled InAs quantum dots. Applied Physics Letters, 1998, 73, 517-519.	1.5	68
548	Terahertz Emission from Quantum Beats in Coupled Quantum Wells. Japanese Journal of Applied Physics, 1998, 37, 1643-1645.	0.8	16
549	Below-Gap Spectroscopy of Undoped GaAs/AlGaAs Quantum Wells by Two-Wavelength Excited Photoluminescence. Japanese Journal of Applied Physics, 1998, 37, 3210-3213.	0.8	10
550	Lasing Emission from an In0.1Ga0.9N Vertical Cavity Surface Emitting Laser. Japanese Journal of Applied Physics, 1998, 37, L1424-L1426.	0.8	73
551	Prospect of Nanostructure Optical Devices.. The Review of Laser Engineering, 1998, 26, 615-619.	0.0	0
552	Special Issue on Prospects of Photonic Functional Devices. The Review of Laser Engineering, 1998, 26, 588-588.	0.0	0
553	Defect Modes in Two-Dimensional Triangular Photonic Crystals. Japanese Journal of Applied Physics, 1997, 36, L120-L123.	0.8	15
554	Phototransistors Using Point Contact Structures. Japanese Journal of Applied Physics, 1997, 36, 1955-1957.	0.8	8
555	Ultrafast energy relaxation in quantum dots through defect states: A lattice-relaxation approach. Physical Review B, 1997, 56, 10423-10427.	1.1	50
556	Vertical Microcavity Lasers with InGaAs/GaAs Quantum Dots Formed by Spinodal Phase Separation. Japanese Journal of Applied Physics, 1997, 36, L357-L360.	0.8	27
557	Photoluminescence studies of GaAs quantum wires with quantum confined Stark effect. Applied Physics Letters, 1997, 70, 646-648.	1.5	37
558	Up-conversion luminescence via a below-gap state in GaAs/AlGaAs quantum wells. Superlattices and Microstructures, 1997, 22, 521-527.	1.4	8

#	Article	IF	Citations
559	Direct observation of the transition from a 2D layer to 3D islands at the initial stage of InGaAs growth on GaAs by AFM. Journal of Crystal Growth, 1997, 170, 563-567.	0.7	17
560	Off-plane angle dependence of photonic band gap in a two-dimensional photonic crystal. IEEE Journal of Quantum Electronics, 1996, 32, 535-542.	1.0	31
561	Rapid carrier relaxation in self-assembledInxGa1â^'xAs/GaAs quantum dots. Physical Review B, 1996, 54, 11532-11538.	1.1	289
562	Femtosecond dynamics of semiconductor-microcavity polaritons in the nonlinear regime. Solid State Communications, 1996, 97, 941-946.	0.9	46
563	Time and spatial resolved photoluminescence from a single quantum dot. Solid-State Electronics, 1996, 40, 537-540.	0.8	7
564	Photoluminescence from point contact structure â€" Direct observation of electron flow. Physica B: Condensed Matter, 1996, 227, 77-81.	1.3	2
565	Light emission from vertical-microcavity quantum dot laser structures. Physica B: Condensed Matter, 1996, 227, 404-406.	1.3	7
566	Ultrafast spectroscopy of carriers and excitons in semiconductor microcavities. Progress in Crystal Growth and Characterization of Materials, 1996, 33, 155-160.	1.8	3
567	Spatially and spectrally resolved imaging of GaAs quantumâ€dot structures using nearâ€field optical technique. Applied Physics Letters, 1996, 69, 827-829.	1.5	49
568	Influence of carrier transport/capture and gain flattening in picosecond pulse generation of InGaAs microcavity lasers. Applied Physics Letters, 1996, 69, 3137-3139.	1.5	2
569	Fabrication and microscopic photoluminescence imaging of ridgeâ€type InGaAs quantum wires grown on a (110) cleaved plane of AlGaAs/GaAs superlattice. Applied Physics Letters, 1996, 69, 1294-1296.	1.5	9
570	Ultrashort lifetime photocarriers in Ge thin films. Applied Physics Letters, 1996, 68, 3419-3421.	1.5	20
571	Magnetic field dependence of exciton oscillator strength by measurements of magnetoexcitonâ€polariton mode splitting in quantum wells with a microcavity. Applied Physics Letters, 1996, 69, 887-889.	1.5	26
572	Direct Observation of Electron Jet from a Point Contact. Japanese Journal of Applied Physics, 1996, 35, 1151-1153.	0.8	6
573	Semiconductor Nanotechonogies and Optical Devices of Next Generarion. The Review of Laser Engineering, 1996, 24, 246-250.	0.0	0
574	Long-term stability following surgical orthodontic treatment of mandibular prognathisms: investigation by means of lateral X-ray cephalogram. Bulletin of Tokyo Dental College, The, 1996, 37, 167-75.	0.1	3
575	Radiative lifetime of localized excitons in GaAs quantum dots. Superlattices and Microstructures, 1995, 17, 73-76.	1.4	5
576	Coherent and incoherent dynamics of excitons in semiconductor microcavities. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1995, 17, 1295-1303.	0.4	24

#	Article	IF	Citations
577	Saturation of photoluminescence quenching under below-gap excitation in a GaAs/AlGaAs quantum well. Journal of Luminescence, 1995, 63, 235-240.	1.5	32
578	Perspective of Semiconductor Lasers: Semiconductor Lasers with Nanostructures and Microcavity.. The Review of Laser Engineering, 1995, 23, 479-486.	0.0	0
579	Observation of a single photoluminescence peak from a single quantum dot. Applied Physics Letters, 1995, 67, 3257-3259.	1.5	33
580	Observation of enhanced lateral confinement of excitons in GaAs quantum wires with various sizes (7â€“30 nm) by magnetophotoluminescence measurements. Applied Physics Letters, 1995, 66, 2502-2504.	1.5	16
581	Formation of InGaAs Quantum Dots on GaAs Multi-Atomic Steps by Metalorganic Chemical Vapor Deposition Growth. Japanese Journal of Applied Physics, 1995, 34, 4376-4379.	0.8	24
582	Cavity optimization for minimum pulsewidth of gain-switched semiconductor lasers. IEEE Photonics Technology Letters, 1995, 7, 272-274.	1.3	7
583	In situ fabrication of selfâ€aligned InGaAs quantum dots on GaAs multiatomic steps by metalorganic chemical vapor deposition. Applied Physics Letters, 1995, 66, 3663-3665.	1.5	164
584	Oneâ€dimensional exciton diffusion in GaAs quantum wires. Applied Physics Letters, 1995, 67, 1535-1537.	1.5	39
585	Epitaxial Growth Controlled in Three Dimensions. Self-Assembling of Quantum Boxes using Stranski-Krastanov Growth Mode.. Hyomen Kagaku, 1995, 16, 624-630.	0.0	0
586	Area Density Control of Quantum-Size InGaAs/Ga(Al)As Dots by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1994, 33, L1634-L1637.	0.8	40
587	GaAs quantum dots with lateral dimension of 25 nm fabricated by selective metalorganic chemical vapor deposition growth. Applied Physics Letters, 1994, 64, 2495-2497.	1.5	63
588	Time-resolved vacuum Rabi oscillations in a semiconductor quantum microcavity. Physical Review B, 1994, 50, 14663-14666.	1.1	195
589	Magnetoexcitons in quantum wires with an anisotropic parabolic potential. Physical Review B, 1994, 50, 7719-7723.	1.1	19
590	Exciton radiative lifetime in GaAs quantum wires grown by metalorganic chemicalâ€vapor selective growth. Applied Physics Letters, 1994, 64, 1564-1566.	1.5	14
591	Demonstration of confined optical field effect in a vertical microcavity by examining the low temperature photonâ€exciton interaction in two kinds of quantum wells. Applied Physics Letters, 1994, 64, 1068-1070.	1.5	21
592	Fabrication of verticalâ€microcavity quantum wire lasers. Applied Physics Letters, 1994, 64, 2200-2202.	1.5	37
593	Fabrication of quantum wires and dots by MOCVD selective growth. Solid-State Electronics, 1994, 37, 523-528.	0.8	57
594	Optical properties of GaAs quantum dots fabricated by MOCVD selective growth. Solid-State Electronics, 1994, 37, 579-581.	0.8	6

#	Article	IF	Citations
595	Highly uniform InGaAs quantum dots (â‰ˆ nm) grown by MOVPE on GaAs. Journal of Crystal Growth, 1994, 145, 986-987.	0.7	10
596	Highly uniform InGaAs/GaAs quantum dots (â¼15 nm) by metalorganic chemical vapor deposition. Applied Physics Letters, 1994, 65, 1421-1423.	1.5	242
597	Polarization dependence of optoelectronic properties in quantum dots and quantum wires-consequences of valence-band mixing. IEEE Journal of Quantum Electronics, 1994, 30, 640-653.	1.0	34
598	Growth process and mechanism of nanometer-scale GaAs dot-structures using MOCVD selective growth. Journal of Crystal Growth, 1993, 126, 707-717.	0.7	49
599	Theoretical analysis of band structures and lasing characteristics in strained quantum wire lasers. IEEE Journal of Quantum Electronics, 1993, 29, 2109-2116.	1.0	17
600	Fabrication and optical properties of GaAs quantum wires and dots by MOCVD selective growth. Semiconductor Science and Technology, 1993, 8, 1082-1088.	1.0	26
601	Fabrication of GaAs quantum wires (â¼10 nm) by metalorganic chemical vapor selective deposition growth. Applied Physics Letters, 1993, 63, 355-357.	1.5	94
602	Near band edge polarization dependence as a probe of structural symmetry in GaAs/AlGaAs quantum dot structures. Applied Physics Letters, 1993, 62, 756-758.	1.5	32
603	Fabrication of InGaAs Strained Quantum Wire Structures Using Selective-Area Metal-Organic Chemical Vapor Deposition Growth. Japanese Journal of Applied Physics, 1993, 32, L1377-L1379.	0.8	30
604	Fabrication of GaAs arrowheadâ€shaped quantum wires by metalorganic chemical vapor deposition selective growth. Applied Physics Letters, 1993, 62, 49-51.	1.5	68
605	Cross Sectional Shape Dependence of Quantum Wire Band Structures and Optical Matrix Elements. Japanese Journal of Applied Physics, 1993, 32, L1592-L1595.	0.8	5
606	Photoluminescence spectra and anisotropic energy shift of GaAs quantum wires in high magnetic fields. Physical Review Letters, 1992, 69, 2963-2966.	2.9	147
607	Selective growth of GaAs wire structures by electron beam induced metalorganic chemical vapor deposition. Applied Physics Letters, 1992, 60, 68-70.	1.5	20
608	Fabrication of GaAs quantum wires on epitaxially grown V grooves by metalâ€organic chemicalâ€vapor deposition. Journal of Applied Physics, 1992, 71, 533-535.	1.1	173
609	Observation of the coupled exciton-photon mode splitting in a semiconductor quantum microcavity. Physical Review Letters, 1992, 69, 3314-3317.	2.9	2,140
610	Quantum wires with strain effect: Tight-binding analysis. Surface Science, 1992, 267, 291-295.	0.8	17
611	Nonlinear gain effects due to carrier heating and spectral holeburning in strained-quantum-well lasers. IEEE Photonics Technology Letters, 1992, 4, 682-685.	1.3	53
612	Consequences of structural disorder on laser properties in quantum wire lasers. IEEE Photonics Technology Letters, 1992, 4, 835-837.	1.3	4

#	Article	IF	Citations
613	MOCVD selective growth of GaAs: C wire and dot structures by electron beam irradiation. Journal of Crystal Growth, 1992, 124, 213-219.	0.7	6
614	Fabrication of InGaAs strained quantum wires using selective MOCVD growth on SiO2-patterned GaAs substrate. Journal of Crystal Growth, 1992, 124, 502-506.	0.7	21
615	Picosecond lasing dynamics of gain-switched quantum well lasers and its dependence on quantum well structures. IEEE Journal of Quantum Electronics, 1991, 27, 1648-1654.	1.0	10
616	Tight binding analysis for quantum-wire lasers and quantum-wire infrared detectors. IEEE Journal of Quantum Electronics, 1991, 27, 1817-1823.	1.0	15
617	Nonlinear gain effects in quantum well, quantum well wire, and quantum well box lasers. IEEE Journal of Quantum Electronics, 1991, 27, 1824-1829.	1.0	29
618	Nonlinear gain effects on spectral dynamics in quantum well lasers. IEEE Photonics Technology Letters, 1991, 3, 106-107.	1.3	11
619	Tight binding analysis of quantum wire structures. Superlattices and Microstructures, 1991, 10, 83-87.	1.4	4
620	Enhanced and inhibited spontaneous emission in GaAs/AlGaAs vertical microcavity lasers with two kinds of quantum wells. Applied Physics Letters, 1991, 58, 2339-2341.	1.5	59
621	Differential gain of GaAs/AlGaAs quantum well and modulationâ€doped quantum well lasers. Applied Physics Letters, 1991, 58, 4-6.	1.5	21
622	Picosecond dynamics in gainâ€switched uncoupled and coupled quantum well lasers. Applied Physics Letters, 1991, 58, 2064-2066.	1.5	4
623	Dependence of lasing characteristics of quantum well lasers on substrate orientation: Tightâ€binding theory. Applied Physics Letters, 1991, 58, 881-883.	1.5	8
624	Wavelength switching of picosecond pulse (<10 ps) in a quantum well laser and its allâ€optical logic gating operations. Applied Physics Letters, 1991, 58, 1709-1711.	1.5	1
625	Tight-binding analysis of energy-band structures in quantum wires. Physical Review B, 1991, 43, 4732-4738.	1.1	46
626	In situpatterning of contamination resists in metalorganic chemical vapor deposition for fabrication of quantum wires. Applied Physics Letters, 1991, 58, 2372-2374.	1.5	6
627	Picosecond spectral dynamics of gainâ€switched quantumâ€well lasers and its dependence on quantumâ€well structures. Journal of Applied Physics, 1990, 67, 2675-2677.	1.1	8
628	Tightâ€binding analysis of the conductionâ€band structure in quantum wires. Applied Physics Letters, 1990, 57, 1224-1226.	1.5	17
629	Theoretical analysis of bistable distributed feedback lasers with detuning effect. Journal of Lightwave Technology, 1990, 8, 1630-1637.	2.7	8
630	Fast bistable wavelength switching characteristics in two-electrode distributed feedback laser. IEEE Photonics Technology Letters, 1990, 2, 109-110.	1.3	15

#	Article	IF	Citations
631	Field spectrum anisotropy in multiple quantum-well semiconductor lasers subjected to high magnetic fields. Superlattices and Microstructures, 1988, 4, 507-510.	1.4	0
632	Observation of a short optical pulse (<1.3 ps) from a gainâ€switched quantum well laser. Applied Physics Letters, 1988, 53, 1580-1582.	1.5	28
633	Picosecond pulse generation in detuned distributed feedback lasers. Electronics Letters, 1988, 24, 170.	0.5	11
634	Process dependence of AlAs/GaAs superlattice mixing induced by silicon implantation. Applied Physics Letters, 1987, 50, 281-283.	1.5	28
635	Reduction of the field spectrum linewidth of a multiple quantum well laser in a high magnetic fieldâ€"spectral properties of quantum dot lasers. Applied Physics Letters, 1987, 50, 365-367.	1.5	22
636	Transmission electron microscopy and photoluminescence study of silicon and boron ion implanted GaAs/GaAlAs quantum wells. Applied Physics Letters, 1987, 50, 92-94.	1.5	10
637	Picosecond pulse generation (<1.8 ps) in a quantum well laser by a gain switching method. Applied Physics Letters, 1987, 51, 1295-1297.	1.5	47
638	Modulation properties of semiconductor lasers.. The Review of Laser Engineering, 1987, 15, 250-257.	0.0	0
639	Ultrafast quantum well optical devices.. The Review of Laser Engineering, 1987, 15, 1011-1015.	0.0	0
640	Quantum well lasers--Gain, spectra, dynamics. IEEE Journal of Quantum Electronics, 1986, 22, 1887-1899.	1.0	524
641	ActiveQswitching in a GaAs/AlGaAs multiquantum well laser with an intracavity monolithic loss modulator. Applied Physics Letters, 1986, 48, 561-563.	1.5	48
642	Dynamic and spectral properties of semiconductor lasers with quantum-well and quantum-wire effects. Surface Science, 1986, 174, 155-162.	0.8	26
643	Photoluminescence of GaAs-AlGaAs multiple quantum well structures under high excitation by a single shot of 30 ps, 532 nm laser. Surface Science, 1986, 174, 272-277.	0.8	2
644	Doseâ€dependent mixing of AlAsâ€GaAs superlattices by Si ion implantation. Applied Physics Letters, 1986, 49, 701-703.	1.5	73
645	Reduction of the spectral linewidth of semiconductor lasers with quantum wire effectsâ€"Spectral properties of GaAlAs double heterostructure lasers in high magnetic fields. Applied Physics Letters, 1986, 48, 384-386.	1.5	33
646	Highâ€speed GaAs/AlGaAs photoconductive detector using apâ€modulationâ€doped multiquantum well structure. Applied Physics Letters, 1986, 48, 1096-1097.	1.5	4
647	Second quantized state lasing of a current pumped single quantum well laser. Applied Physics Letters, 1986, 49, 1689-1691.	1.5	80
648	Hot photoluminescence of GaAs-AlGaAs multiple quantum well structures under high excitation by a single shot of 30 ps, 532 nm laser. Solid State Communications, 1985, 55, 311-315.	0.9	24

#	Article	IF	Citations
649	Light emission from zeroâ€dimensional excitonsâ€”Photoluminescence from quantum wells in strong magnetic fields. Applied Physics Letters, 1985, 46, 83-85.	1.5	40
650	Recombination lifetime of carriers in GaAsâ€GaAlAs quantum wells near room temperature. Applied Physics Letters, 1985, 46, 519-521.	1.5	64
651	Fermi energy dependence of linewidth enhancement factor of GaAlAs buried heterostructure lasers. Applied Physics Letters, 1985, 47, 905-907.	1.5	23
652	Theory of gain, modulation response, and spectral linewidth in AlGaAs quantum well lasers. IEEE Journal of Quantum Electronics, 1985, 21, 1666-1674.	1.0	241
653	Enhanced modulation bandwidth of GaAlAs double heterostructure lasers in high magnetic fields: Dynamic response with quantum wire effects. Applied Physics Letters, 1985, 47, 1142-1144.	1.5	42
654	Use of high magnetic fields to estimate carrier leakage current in GaInAsPâ€InP double heterostructure lasers. Applied Physics Letters, 1984, 45, 7-9.	1.5	1
655	Quantum noise and dynamics in quantum well and quantum wire lasers. Applied Physics Letters, 1984, 45, 950-952.	1.5	237
656	Two-dimensional quantum-mechanical confinement of electrons in LED by strong magnetic fields. IEEE Transactions on Electron Devices, 1983, 30, 330-334.	1.6	4
657	Two-dimensional quantum-mechanical confinement of electrons in DH lasers by strong magnetic fields. IEEE Journal of Quantum Electronics, 1983, 19, 1255-1257.	1.0	4
658	Spontaneous Emission Characteristics of Quantum Well Lasers in Strong Magnetic Fields -- An Approach to Quantum-Well-Box Light Source --. Japanese Journal of Applied Physics, 1983, 22, L804-L806.	0.8	38
659	Characteristics of Double-Heterostructure Lasers in Strong Magnetic Fields. Japanese Journal of Applied Physics, 1983, 22, 283.	0.8	4
660	Quantum-chemical and physico-chemical properties of hydrochlorothiazide. Arzneimittelforschung, 1983, 33, 688-91.	0.5	0
661	Multidimensional quantum well laser and temperature dependence of its threshold current. Applied Physics Letters, 1982, 40, 939-941.	1.5	3,197
662	Eâ€band InAs/GaAs Triâ€layer Quantum Dot Lasers. Physica Status Solidi (A) Applications and Materials Science, 0, , 2100419.	0.8	0
663	III-V/Si hybrid photonic devices by direct fusion bonding. , 0, .		1